



ISO7831x High-Performance, 8000-V_{PK} Reinforced Triple Digital Isolators

1 Features

- Signaling Rate: Up to 100 Mbps
- Wide Supply Range: 2.25 V to 5.5 V
- 2.25 V to 5.5 V Level Translation
- Wide Temperature Range: –55°C to 125°C
- Low Power Consumption, Typical 1.7 mA per Channel at 1 Mbps
- Low Propagation Delay: 11 ns Typical (5-V Supplies)
- Industry leading CMTI (min): ±100 kV/μs
- Robust Electromagnetic Compatibility (EMC)
- System-Level ESD, EFT, and Surge Immunity
- Low Emissions
- Isolation Barrier Life: > 40 Years
- SOIC-16 Wide Body (DW) and Extra-Wide Body (DWW) Package Options
- Safety-Related Certifications:
 - 8000 V_{PK} Reinforced Isolation per DIN V VDE V 0884-10 (VDE V 0884-10):2006-12
 - 5.7 kV_{RMS} Isolation for 1 Minute per UL 1577
 - CSA Component Acceptance Notice 5A, IEC 60950-1 and IEC 60601-1 End Equipment Standards
 - CQC Certification per GB4943.1-2011
 - TUV Certification per EN 61010-1 and EN 60950-1
 - All DW Package Certifications Complete; DWW Package Certifications Complete per UL, VDE, TUV and Planned for CSA and CQC

2 Applications

- Industrial Automation
- Motor Control
- Power Supplies
- Solar Inverters
- Medical Equipment
- Hybrid Electric Vehicles

3 Description

The ISO7831x device is a high-performance, 3-channel digital isolator with 8000-V_{PK} isolation voltage. This device has reinforced isolation certifications according to VDE, CSA, TUV and CQC. The isolator provides high electromagnetic immunity and low emissions at low power consumption, while isolating CMOS or LVCMOS digital I/Os.

Each isolation channel has a logic input and output buffer separated by silicon dioxide (SiO₂) insulation barrier. This device comes with enable pins which can be used to put the respective outputs in high impedance for multi-master driving applications and to reduce power consumption. The ISO7831x device has two forward and one reverse-direction channels. If the input power or signal is lost, the default output is *high* for the ISO7831 device and *low* for the ISO7831F device. See [Device Functional Modes](#) for further details.

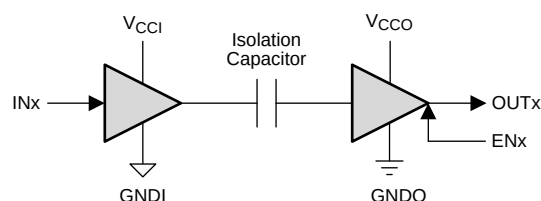
Used in conjunction with isolated power supplies, this device helps prevent noise currents on a data bus or other circuits from entering the local ground and interfering with or damaging sensitive circuitry. Through innovative chip design and layout techniques, electromagnetic compatibility of ISO7831x has been significantly enhanced to ease system-level ESD, EFT, surge, and emissions compliance. ISO7831x is available in a 16-pin SOIC wide-body (DW) and extra-wide body (DWW) packages.

Device Information⁽¹⁾

PART NUMBER	PACKAGE	BODY SIZE (NOM)
ISO7831	DW (16)	10.30 mm × 7.50 mm
ISO7831F	DWW (16)	10.30 mm × 14.0 mm

(1) For all available packages, see the orderable addendum at the end of the data sheet.

Simplified Schematic



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V_{CCI} and GNDI are supply and ground connections respectively for the input channels.

V_{CCO} and GNDO are supply and ground connections respectively for the output channels.



Table of Contents

1 Features	1	6.19 Typical Characteristics	15
2 Applications	1	7 Parameter Measurement Information	16
3 Description	1	8 Detailed Description	18
4 Revision History	2	8.1 Overview	18
5 Pin Configuration and Functions	4	8.2 Functional Block Diagram	18
6 Specifications	5	8.3 Feature Description	19
6.1 Absolute Maximum Ratings	5	8.4 Device Functional Modes	20
6.2 ESD Ratings	5	9 Application and Implementation	21
6.3 Recommended Operating Conditions	5	9.1 Application Information	21
6.4 Thermal Information	6	9.2 Typical Application	21
6.5 Power Rating	6	10 Power Supply Recommendations	23
6.6 Insulation Characteristics	7	11 Layout	24
6.7 Regulatory Information	8	11.1 Layout Guidelines	24
6.8 Safety Limiting Values	8	11.2 Layout Example	24
6.9 Electrical Characteristics—5-V Supply	9	12 Device and Documentation Support	25
6.10 Supply Current Characteristics—5-V Supply	9	12.1 Documentation Support	25
6.11 Electrical Characteristics—3.3-V Supply	10	12.2 Related Links	25
6.12 Supply Current Characteristics—3.3-V Supply	10	12.3 Receiving Notification of Documentation Updates	25
6.13 Electrical Characteristics—2.5-V Supply	11	12.4 Community Resources	25
6.14 Supply Current Characteristics—2.5-V Supply	11	12.5 Trademarks	25
6.15 Switching Characteristics—5-V Supply	12	12.6 Electrostatic Discharge Caution	25
6.16 Switching Characteristics—3.3-V Supply	12	12.7 Glossary	25
6.17 Switching Characteristics—2.5-V Supply	13	13 Mechanical, Packaging, and Orderable Information	26
6.18 Insulation Characteristics Curves	14		

4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from Revision A (September 2015) to Revision B	Page
• Changed Features From: Low Power Consumption, Typical 2.5 mA per Channel at 1 Mbps To: Low Power Consumption, Typical 1.7 mA per Channel at 1 Mbps	1
• Changed the isolation barrier life from > 25 years to > 40 years in the Features section	1
• Changed Features From: Safety and Regulatory Approvals To: Safety-Related Certifications	1
• Updated the status of the certifications throughout the document	1
• Added the extra-wide body package (16 pin SOIC [DWW]) option	1
• Changed the values for the DW package in the <i>Thermal Information</i> table	6
• Moved Insulation Characteristics to the Specifications section	7
• Changed C _{IO} Specification From: 2 pF To: ~1 pF	7
• Added the climatic category parameter to the <i>Insulation Characteristics</i> table	7
• Moved Regulatory Information to the Specifications section	8
• Moved Safety Limiting Values to the Specifications section	8
• Changed the test conditions and values for the DW package in the <i>Safety Limiting Values</i> table	8
• Changed V _{CCO} to V _{CCI} in the minimum value for the input threshold voltage hysteresis parameter in the electrical characteristics tables	9
• Added the V _{CM} test condition to the CMTI parameter in the electrical characteristics tables. Also updated the minimum value from 70 to 100 and deleted the maximum value of 100	9
• Changed t _{IS} To: t _{DO} in Switching Characteristics—5-V Supply	12
• Changed t _{IS} To: t _{DO} in Switching Characteristics—3.3-V Supply	12
• Changed t _{IS} To: t _{DO} in Switching Characteristics—2.5-V Supply	13
• Added the lifetime projection graphs for DW and DWW packages to the Insulation Characteristics Curves section	14

Revision History (continued)

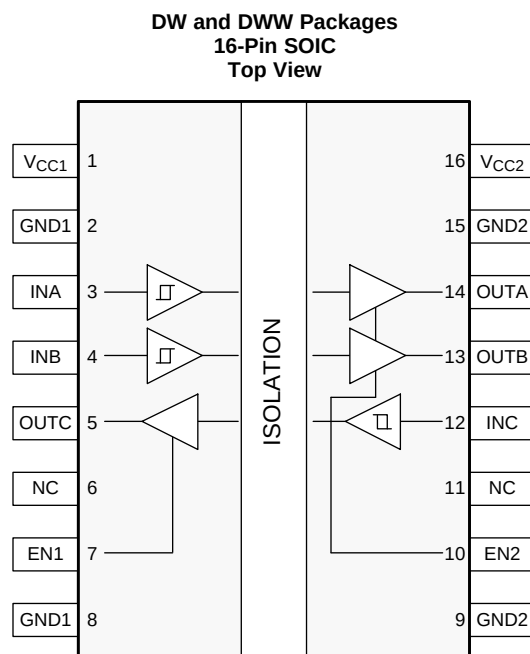
- Changed the thermal derating curves in the *Safety Limiting Values* section [14](#)
- Changed 2.7 V To: 1.7 V, fs high To: default high, and fs low To: default low in [Figure 15](#) [17](#)

Changes from Original (July 2015) to Revision A

Page

- Changed From: 1-page Product Preview To: Production datasheet..... [1](#)

5 Pin Configuration and Functions



Pin Functions

PIN		I/O	DESCRIPTION
NAME	NO.		
EN1	7	I	Output enable 1. Output pin on side 1 is enabled when EN1 is high or open and in high-impedance state when EN1 is low.
EN2	10	I	Output enable 2. Output pins on side 2 are enabled when EN2 is high or open and in high-impedance state when EN2 is low.
GND1	2, 8	—	Ground connection for V _{CC1}
GND2	9, 15	—	Ground connection for V _{CC2}
INA	3	I	Input, channel A
INB	4	I	Input, channel B
INC	12	I	Input, channel C
OUTA	14	O	Output, channel A
OUTB	13	O	Output, channel B
OUTC	5	O	Output, channel C
NC	6, 11	—	Not connected
V _{CC1}	1	—	Power supply, side 1
V _{CC2}	16	—	Power supply, side 2

6 Specifications

6.1 Absolute Maximum Ratings

See ⁽¹⁾

		MIN	MAX	UNIT
V_{CC1} V_{CC2}	Supply voltage ⁽²⁾	–0.5	6	V
V	Voltage at INx, OUTx, or ENx	–0.5	$V_{CCx} + 0.5^{(3)}$	V
I_O	Output current	–15	15	mA
T_J	Junction temperature	–55	150	°C
T_{stg}	Storage temperature	–65	150	°C

- (1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) All voltage values except differential I/O bus voltages are with respect to the local ground terminal (GND1 or GND2) and are peak voltage values.
- (3) Maximum voltage must not exceed 6 V

6.2 ESD Ratings

		VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	±6000
		Charged device model (CDM), per JEDEC specification JESD22-C101 ⁽²⁾	±1500

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

		MIN	NOM	MAX	UNIT
V_{CC1} , V_{CC2}	Supply voltage	2.25		5.5	V
I_{OH}	High-level output current	$V_{CCO}^{(1)} = 5\text{ V}$	–4		mA
		$V_{CCO}^{(1)} = 3.3\text{ V}$	–2		
		$V_{CCO}^{(1)} = 2.5\text{ V}$	–1		
I_{OL}	Low-level output current	$V_{CCO}^{(1)} = 5\text{ V}$		4	mA
		$V_{CCO}^{(1)} = 3.3\text{ V}$		2	
		$V_{CCO}^{(1)} = 2.5\text{ V}$		1	
V_{IH}	High-level input voltage	$0.7 \times V_{CCI}^{(1)}$		$V_{CCI}^{(1)}$	V
V_{IL}	Low-level input voltage	0		$0.3 \times V_{CCI}^{(1)}$	V
DR	Signaling rate	0		100	Mbps
T_A	Ambient temperature	–55	25	125	°C

- (1) V_{CCI} = Input-side V_{CC} ; V_{CCO} = Output-side V_{CC} .

6.4 Thermal Information

THERMAL METRIC ⁽¹⁾		ISO7831		UNIT
		DW (SOIC)	DWW (SOIC)	
		16 PINS	16 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	81.1	83.4	°C/W
$R_{\theta JC(top)}$	Junction-to-case(top) thermal resistance	43.8	45.2	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	45.7	54.1	°C/W
ψ_{JT}	Junction-to-top characterization parameter	17.0	17.6	°C/W
ψ_{JB}	Junction-to-board characterization parameter	45.2	53.3	°C/W
$R_{\theta JC(bottom)}$	Junction-to-case(bottom) thermal resistance	—	—	°C/W

(1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC Package Thermal Metrics](#) application report.

6.5 Power Rating

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
P_D	Maximum power dissipation			150	mW
P_{D1}	Maximum power dissipation by side-1			50	mW
P_{D2}	Maximum power dissipation by side-2			100	mW

6.6 Insulation Characteristics

PARAMETER		TEST CONDITIONS	SPECIFICATION		UNIT
			DW	DWW	
CLR	External clearance ⁽¹⁾	Shortest terminal-to-terminal distance through air	>8	>14.5	mm
CPG	External creepage ⁽¹⁾	Shortest terminal-to-terminal distance across the package surface	>8	>14.5	mm
DTI	Distance through the insulation	Minimum internal gap (internal clearance)	>21	>21	μm
CTI	Comparative tracking index	DIN EN 60112 (VDE 0303-11); IEC 60112; UL 746A	>600	>600	V
Material group			I	I	
Overvoltage category per IEC 60664-1		Rated mains voltage ≤ 600 V _{RMS}	I–IV	I–IV	
		Rated mains voltage ≤ 1000 V _{RMS}	I–III	I–IV	
DIN V VDE V 0884–10 (VDE V 0884–10):2006-12⁽²⁾					
V _{IOWM}	Maximum isolation working voltage	Time dependent dielectric breakdown (TDDB) Test; see Figure 1 and Figure 2	1500	2000	V _{RMS}
			2121	2828	V _{DC}
V _{IOTM}	Maximum transient isolation voltage	V _{TEST} = V _{IOTM} t = 60 s (qualification) t = 1 s (100% production)	8000	8000	V _{PK}
V _{IOSM}	Maximum surge isolation voltage for reinforced insulation ⁽³⁾	Test method per IEC 60065, 1.2/50 μs waveform, V _{TEST} = 1.6 × V _{IOSM} = 12800 V _{PK} (qualification)	8000	8000	V _{PK}
V _{IORM}	Maximum repetitive peak isolation voltage		2121	2828	V _{PK}
V _{PR}	Input-to-output test voltage	Method a, After Input/Output safety test subgroup 2/3, V _{PR} = V _{IORM} × 1.2, t = 10 s, Partial discharge < 5 pC	2545	3394	V _{PK}
		Method a, After environmental tests subgroup 1, V _{PR} = V _{IORM} × 1.6, t = 10 s, Partial Discharge < 5 pC	3394	4525	
		Method b1, V _{PR} = V _{IORM} × 1.875, t = 1 s (100% Production test) Partial discharge < 5 pC	3977	5303	
C _{IO}	Barrier capacitance, input to output ⁽⁴⁾	V _{IO} = 0.4 × sin (2πft), f = 1 MHz	~1	~1	pF
R _{IO}	Isolation resistance, input to output ⁽⁴⁾	V _{IO} = 500 V, T _A = 25°C	>10 ¹²	>10 ¹²	Ω
		V _{IO} = 500 V, 100°C ≤ T _A ≤ max	>10 ¹¹	>10 ¹¹	Ω
R _S	Isolation resistance	V _{IO} = 500 V at T _S	>10 ⁹	>10 ⁹	Ω
Pollution degree			2	2	
Climatic category			55/125/21	55/125/21	
UL 1577					
V _{ISO}	Withstanding isolation voltage	V _{TEST} = V _{ISO} = 5700 V _{RMS} , t = 60 s (qualification), V _{TEST} = 1.2 × V _{ISO} = 6840 V _{RMS} , t = 1 s (100% production)	5700	5700	V _{RMS}

- (1) Creepage and clearance requirements should be applied according to the specific equipment isolation standards of an application. Care should be taken to maintain the creepage and clearance distance of a board design to ensure that the mounting pads of the isolator on the printed-circuit board do not reduce this distance. Creepage and clearance on a printed-circuit board become equal in certain cases. Techniques such as inserting grooves and/or ribs on a printed circuit board are used to help increase these specifications
- (2) This coupler is suitable for *safe electrical insulation* only within the safety ratings. Compliance with the safety ratings shall be ensured by means of suitable protective circuits.
- (3) Testing is carried out in air or oil to determine the intrinsic surge immunity of the isolation barrier.
- (4) All pins on each side of the barrier tied together creating a two-terminal device.

6.7 Regulatory Information

All DW package certifications are complete. DWW package certifications are complete for UL, VDE and TUV and planned for CSA and CQC.

VDE	CSA	UL	CQC	TUV
Certified according to DIN V VDE V 0884-10 (VDE V 0884-10):2006-12 and DIN EN 60950-1 (VDE 0805 Teil 1):2011-01	Approved under CSA Component Acceptance Notice 5A, IEC 60950-1 and IEC 60601-1	Certified according to UL 1577 Component Recognition Program	Certified according to GB 4943.1-2011	Certified according to EN 61010-1:2010 (3rd Ed) and EN 60950-1:2006/A11:2009/A1:2010/A12:2011/A2:2013
Reinforced insulation Maximum transient isolation voltage, 8000 V _{PK} ; Maximum repetitive peak isolation voltage, 2121 V _{PK} (DW), 2828 V _{PK} (DWW); Maximum surge isolation voltage, 8000 V _{PK}	Reinforced insulation per CSA 60950-1-07+A1+A2 and IEC 60950-1 2nd Ed., 800 V _{RMS} (DW) and 1450 V _{RMS} (DWW) maximum working voltage (pollution degree 2, material group I); 2 MOPP (Means of Patient Protection) per CSA 60601-1:14 and IEC 60601-1 Ed. 3.1, 250 V _{RMS} (354 V _{PK}) maximum working voltage	Single protection, 5700 V _{RMS}	Reinforced Insulation, Altitude ≤ 5000 m, Tropical Climate, 250 V _{RMS} maximum working voltage	5700 V _{RMS} Reinforced insulation per EN 61010-1:2010 (3rd Ed) up to working voltage of 600 V _{RMS} (DW package) and 1000 V _{RMS} (DWW package) 5700 V _{RMS} Reinforced insulation per EN 60950-1:2006/A11:2009/A1:2010/A12:2011/A2:2013 up to working voltage of 800 V _{RMS} (DW package) and 1450 V _{RMS} (DWW package)
Certificate number: 40040142	Master contract number: 220991	File number: E181974	Certificate number: CQC15001121716	Client ID number: 77311

6.8 Safety Limiting Values

Safety limiting intends to minimize potential damage to the isolation barrier upon failure of input or output circuitry. A failure of the I/O can allow low resistance to ground or the supply and, without current limiting, dissipate sufficient power to overheat the die and damage the isolation barrier potentially leading to secondary system failures.

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
DW PACKAGE					
I _S Safety input, output, or supply current	R _{θJA} = 81.1°C/W, V _I = 5.5 V, T _J = 150°C, T _A = 25°C, see Figure 3			280	mA
	R _{θJA} = 81.1°C/W, V _I = 3.6 V, T _J = 150°C, T _A = 25°C, see Figure 3			428	
	R _{θJA} = 81.1°C/W, V _I = 2.75 V, T _J = 150°C, T _A = 25°C, see Figure 3			560	
P _S Safety input, output, or total power	R _{θJA} = 81.1°C/W, T _J = 150°C, T _A = 25°C, see Figure 5			1541	mW
T _S Maximum safety temperature				150	°C
DWW PACKAGE					
I _S Safety input, output, or supply current	R _{θJA} = 83.4°C/W, V _I = 5.5 V, T _J = 150°C, T _A = 25°C, see Figure 4			273	mA
	R _{θJA} = 83.4°C/W, V _I = 3.6 V, T _J = 150°C, T _A = 25°C, see Figure 4			416	
	R _{θJA} = 83.4°C/W, V _I = 2.75 V, T _J = 150°C, T _A = 25°C, see Figure 4			545	
P _S Safety input, output, or total power	R _{θJA} = 83.4°C/W, T _J = 150°C, T _A = 25°C, see Figure 6			1499	mW
T _S Maximum safety temperature				150	°C

The maximum safety temperature is the maximum junction temperature specified for the device. The power dissipation and junction-to-air thermal impedance of the device installed in the application hardware determines the junction temperature. The assumed junction-to-air thermal resistance in the [Thermal Information](#) is that of a device installed on a high-K test board for leaded surface mount packages. The power is the recommended maximum input voltage times the current. The junction temperature is then the ambient temperature plus the power times the junction-to-air thermal resistance.

6.9 Electrical Characteristics—5-V Supply

 $V_{CC1} = V_{CC2} = 5\text{ V} \pm 10\%$ (over recommended operating conditions unless otherwise noted)

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
V_{OH}	High-level output voltage $I_{OH} = -4\text{ mA}$; see Figure 13	$V_{CCO}^{(1)} - 0.4$	$V_{CCO} - 0.2$		V
V_{OL}	Low-level output voltage $I_{OL} = 4\text{ mA}$; see Figure 13		0.2	0.4	V
$V_{I(HYS)}$	Input threshold voltage hysteresis	$0.1 \times V_{CCI}^{(1)}$			V
I_{IH}	High-level input current $V_{IH} = V_{CCI}$ at INx or ENx			10	μA
I_{IL}	Low-level input current $V_{IL} = 0\text{ V}$ at INx or ENx	-10			μA
CMTI	Common-mode transient immunity $V_I = V_{CCI}$ or 0 V , $V_{CM} = 1500\text{ V}$; see Figure 16	100			kV/ μs
C_I	Input capacitance ⁽²⁾ $V_I = V_{CC} / 2 + 0.4 \times \sin(2\pi ft)$, $f = 1\text{ MHz}$, $V_{CC} = 5\text{ V}$		2		pF

(1) V_{CCI} = Input-side V_{CC} ; V_{CCO} = Output-side V_{CC} .

(2) Measured from input pin to ground.

6.10 Supply Current Characteristics—5-V Supply

 $V_{CC1} = V_{CC2} = 5\text{ V} \pm 10\%$ (over recommended operating conditions unless otherwise noted)

PARAMETER	TEST CONDITIONS	SUPPLY CURRENT	MIN	TYP	MAX	UNIT
Supply current - disable	EN1 = EN2 = 0 V , $V_I = 0\text{ V}$ (Devices with suffix F), $V_I = V_{CCI}$ (Devices without suffix F)	I_{CC1}		1	1.6	mA
		I_{CC2}		0.8	1.3	
	EN2 = 0 V , $V_I = V_{CCI}$ (Devices with suffix F), $V_I = 0\text{ V}$ (Devices without suffix F)	I_{CC1}		3.3	4.8	
		I_{CC2}		2	2.9	
Supply current - DC signal	$V_I = 0\text{ V}$ (Devices with suffix F), $V_I = V_{CCI}$ (Devices without suffix F)	I_{CC1}		1.4	2.3	
		I_{CC2}		1.7	2.6	
	$V_I = V_{CCI}$ (Devices with suffix F), $V_I = 0\text{ V}$ (Devices without suffix F)	I_{CC1}		3.8	5.6	
		I_{CC2}		3	4.3	
Supply current - AC signal	All channels switching with square wave clock input; $C_L = 15\text{ pF}$	1 Mbps		2.6	4	
				2.4	3.6	
		10 Mbps		3.2	4.5	
				3.4	4.6	
		100 Mbps		8.7	10.5	
				13.2	15.8	

6.11 Electrical Characteristics—3.3-V Supply

$V_{CC1} = V_{CC2} = 3.3 \text{ V} \pm 10\%$ (over recommended operating conditions unless otherwise noted)

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
V_{OH} High-level output voltage	$I_{OH} = -2 \text{ mA}$; see Figure 13	$V_{CCO}^{(1)} - 0.4$	$V_{CCO} - 0.2$		V
V_{OL} Low-level output voltage	$I_{OL} = 2 \text{ mA}$; see Figure 13		0.2	0.4	V
$V_{I(HYS)}$ Input threshold voltage hysteresis		$0.1 \times V_{CCI}^{(1)}$			V
I_{IH} High-level input current	$V_{IH} = V_{CCI}$ at INx or ENx			10	μA
I_{IL} Low-level input current	$V_{IL} = 0 \text{ V}$ at INx or ENx	–10			μA
CMTI Common-mode transient immunity	$V_I = V_{CCI}$ or 0 V , $V_{CM} = 1500 \text{ V}$; see Figure 16	100			kV/ μs

(1) V_{CCI} = Input-side V_{CC} ; V_{CCO} = Output-side V_{CC} .

6.12 Supply Current Characteristics—3.3-V Supply

$V_{CC1} = V_{CC2} = 3.3 \text{ V} \pm 10\%$ (over recommended operating conditions unless otherwise noted)

PARAMETER	TEST CONDITIONS	SUPPLY CURRENT	MIN	TYP	MAX	UNIT
Supply current - disable	$EN1 = EN2 = 0 \text{ V}$, $V_I = 0 \text{ V}$ (Devices with suffix F), $V_I = V_{CCI}$ (Devices without suffix F)	I_{CC1}		1	1.6	mA
		I_{CC2}		0.8	1.3	
	$EN1 = EN2 = 0 \text{ V}$, $V_I = V_{CCI}$ (Devices with suffix F), $V_I = 0 \text{ V}$ (Devices without suffix F)	I_{CC1}		3.3	4.8	
		I_{CC2}		1.9	2.9	
Supply current - DC signal	$V_I = 0 \text{ V}$ (Devices with suffix F), $V_I = V_{CCI}$ (Devices without suffix F)	I_{CC1}		1.4	2.3	
		I_{CC2}		1.7	2.6	
	$V_I = V_{CCI}$ (Devices with suffix F), $V_I = 0 \text{ V}$ (Devices without suffix F)	I_{CC1}		3.8	5.6	
		I_{CC2}		2.9	4.3	
Supply current - AC signal	All channels switching with square wave clock input; $C_L = 15 \text{ pF}$	1 Mbps	I_{CC1}	2.6	4	
			I_{CC2}	2.4	3.5	
		10 Mbps	I_{CC1}	3	4.3	
			I_{CC2}	3.1	4.3	
		100 Mbps	I_{CC1}	6.9	8.3	
			I_{CC2}	10.1	12.2	

6.13 Electrical Characteristics—2.5-V Supply

 $V_{CC1} = V_{CC2} = 2.5 \text{ V} \pm 10\%$ (over recommended operating conditions unless otherwise noted)

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
V_{OH} High-level output voltage	$I_{OH} = -1 \text{ mA}$; see Figure 13	$V_{CCO}^{(1)} - 0.4$	$V_{CCO} - 0.2$		V
V_{OL} Low-level output voltage	$I_{OL} = 1 \text{ mA}$; see Figure 13		0.2	0.4	V
$V_{I(HYS)}$ Input threshold voltage hysteresis		$0.1 \times V_{CCI}^{(1)}$			V
I_{IH} High-level input current	$V_{IH} = V_{CC1}$ at INx or ENx			10	μA
I_{IL} Low-level input current	$V_{IL} = 0 \text{ V}$ at INx or ENx	-10			μA
CMTI Common-mode transient immunity	$V_I = V_{CC1}$ or 0 V , $V_{CM} = 1500 \text{ V}$; see Figure 16	100			kV/ μs

(1) V_{CCI} = Input-side V_{CC} ; V_{CCO} = Output-side V_{CC} .

6.14 Supply Current Characteristics—2.5-V Supply

 $V_{CC1} = V_{CC2} = 2.5 \text{ V} \pm 10\%$ (over recommended operating conditions unless otherwise noted)

PARAMETER	TEST CONDITIONS	SUPPLY CURRENT	MIN	TYP	MAX	UNIT
Supply current - disable	$EN1 = EN2 = 0 \text{ V}$, $V_I = 0 \text{ V}$ (Devices with suffix F), $V_I = V_{CCI}$ (Devices without suffix F)	I_{CC1}		0.9	1.6	mA
		I_{CC2}		0.8	1.3	
	$EN1 = EN2 = 0 \text{ V}$, $V_I = V_{CCI}$ (Devices with suffix F), $V_I = 0 \text{ V}$ (Devices without suffix F)	I_{CC1}		3.3	4.8	
		I_{CC2}		1.9	2.9	
Supply current - DC signal	$V_I = 0 \text{ V}$ (Devices with suffix F), $V_I = V_{CCI}$ (Devices without suffix F)	I_{CC1}		1.4	2.3	
		I_{CC2}		1.7	2.6	
	$V_I = V_{CCI}$ (Devices with suffix F), $V_I = 0 \text{ V}$ (Devices without suffix F)	I_{CC1}		3.8	5.6	
		I_{CC2}		2.9	4.3	
Supply current - AC signal	All channels switching with square wave clock input; $C_L = 15 \text{ pF}$	1 Mbps	I_{CC1}	2.6	4	
			I_{CC2}	2.3	3.5	
		10 Mbps	I_{CC1}	2.9	4.3	
			I_{CC2}	2.9	4.1	
		100 Mbps	I_{CC1}	5.8	7.2	
			I_{CC2}	8.2	10	

6.15 Switching Characteristics—5-V Supply

 $V_{CC1} = V_{CC2} = 5\text{ V} \pm 10\%$ (over recommended operating conditions unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
t_{PLH} , t_{PHL}	Propagation delay time	See Figure 13	6	11	16	ns
PWD	Pulse width distortion ⁽¹⁾ $ t_{PHL} - t_{PLH} $			0.55	4.1	ns
$t_{sk(o)}$	Channel-to-channel output skew time ⁽²⁾	Same-direction channels			2.5	ns
$t_{sk(pp)}$	Part-to-part skew time ⁽³⁾				4.5	ns
t_r	Output signal rise time	See Figure 13		1.7	3.9	ns
t_f	Output signal fall time			1.9	3.9	ns
t_{PHZ}	Disable propagation delay, high-to-high impedance output	See Figure 14		12	20	ns
t_{PLZ}	Disable propagation delay, low-to-high impedance output			12	20	ns
t_{PZH}	Enable propagation delay, high impedance-to-high output for ISO7831			10	20	ns
	Enable propagation delay, high impedance-to-high output for ISO7831F			2	2.5	μs
t_{PZL}	Enable propagation delay, high impedance-to-low output for ISO7831			2	2.5	μs
	Enable propagation delay, high impedance-to-low output for ISO7831F			10	20	ns
t_{DO}	Default output delay time from input power loss	Measured from the time V_{CC} goes below 1.7 V. See Figure 15		0.2	9	μs
t_e	Time interval error	$2^{16} - 1$ PRBS data at 100 Mbps		0.90		ns

- (1) Also known as pulse skew.
- (2) $t_{sk(o)}$ is the skew between outputs of a single device with all driving inputs connected together and the outputs switching in the same direction while driving identical loads.
- (3) $t_{sk(pp)}$ is the magnitude of the difference in propagation delay times between any terminals of different devices switching in the same direction while operating at identical supply voltages, temperature, input signals and loads.

6.16 Switching Characteristics—3.3-V Supply

 $V_{CC1} = V_{CC2} = 3.3\text{ V} \pm 10\%$ (over recommended operating conditions unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
t_{PLH} , t_{PHL}	Propagation delay time	See Figure 13	6	10.8	16	ns
PWD	Pulse width distortion ⁽¹⁾ $ t_{PHL} - t_{PLH} $			0.7	4.2	ns
$t_{sk(o)}$	Channel-to-channel output skew time ⁽²⁾	Same-direction channels			2.2	ns
$t_{sk(pp)}$	Part-to-part skew time ⁽³⁾				4.5	ns
t_r	Output signal rise time	See Figure 13		0.8	3	ns
t_f	Output signal fall time			0.8	3	ns
t_{PHZ}	Disable propagation delay, high-to-high impedance output	See Figure 14		17	32	ns
t_{PLZ}	Disable propagation delay, low-to-high impedance output			17	32	ns
t_{PZH}	Enable propagation delay, high impedance-to-high output for ISO7831			17	32	ns
	Enable propagation delay, high impedance-to-high output for ISO7831F			2	2.5	μs
t_{PZL}	Enable propagation delay, high impedance-to-low output for ISO7831			2	2.5	μs
	Enable propagation delay, high impedance-to-low output for ISO7831F			17	32	ns
t_{DO}	Default output delay time from input power loss	Measured from the time V_{CC} goes below 1.7 V. See Figure 15		0.2	9	μs
t_e	Time interval error	$2^{16} - 1$ PRBS data at 100 Mbps		0.91		ns

- (1) Also known as pulse skew.
- (2) $t_{sk(o)}$ is the skew between outputs of a single device with all driving inputs connected together and the outputs switching in the same direction while driving identical loads.
- (3) $t_{sk(pp)}$ is the magnitude of the difference in propagation delay times between any terminals of different devices switching in the same direction while operating at identical supply voltages, temperature, input signals and loads.

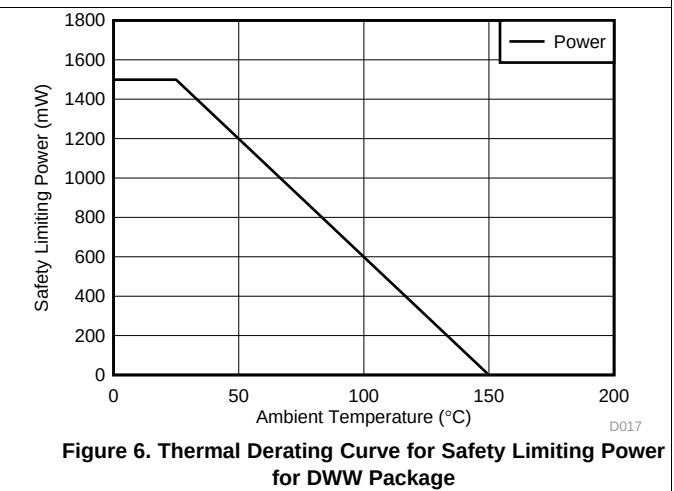
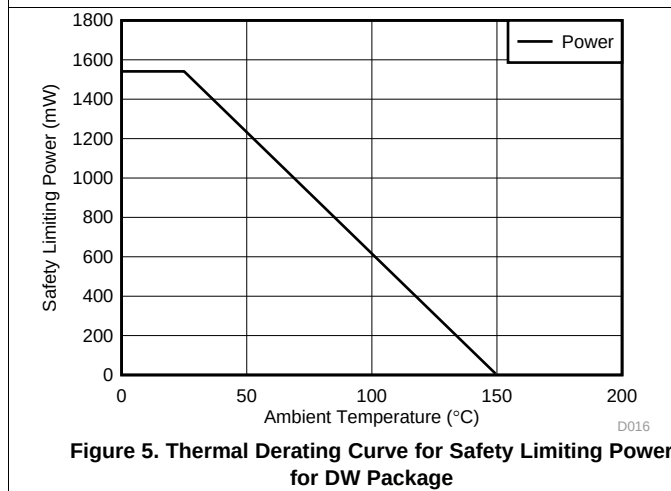
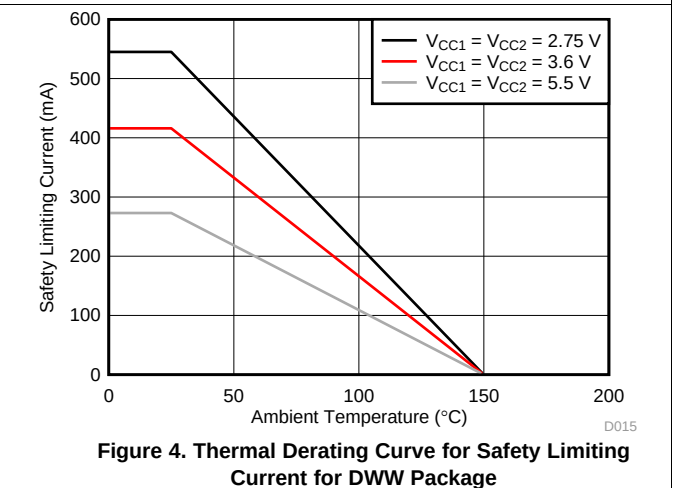
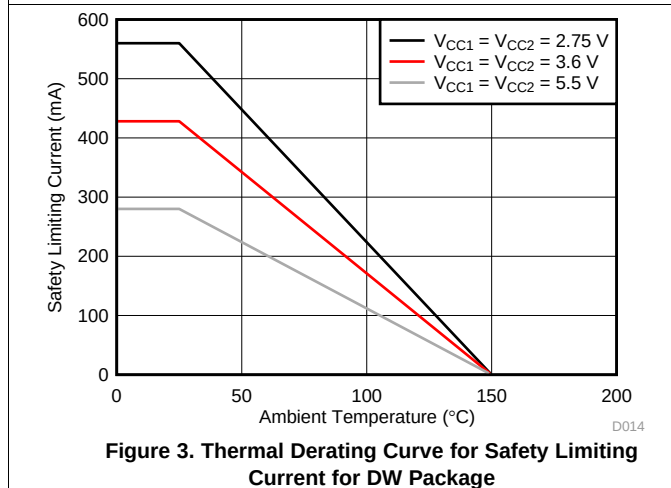
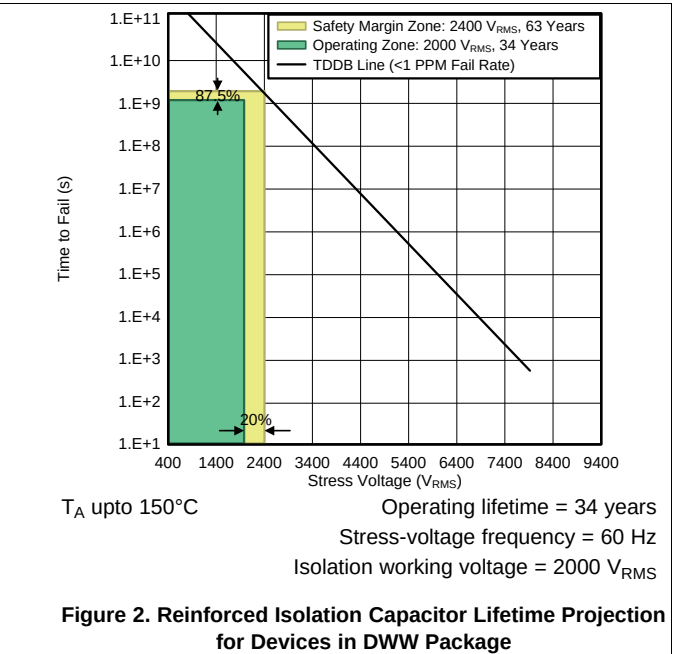
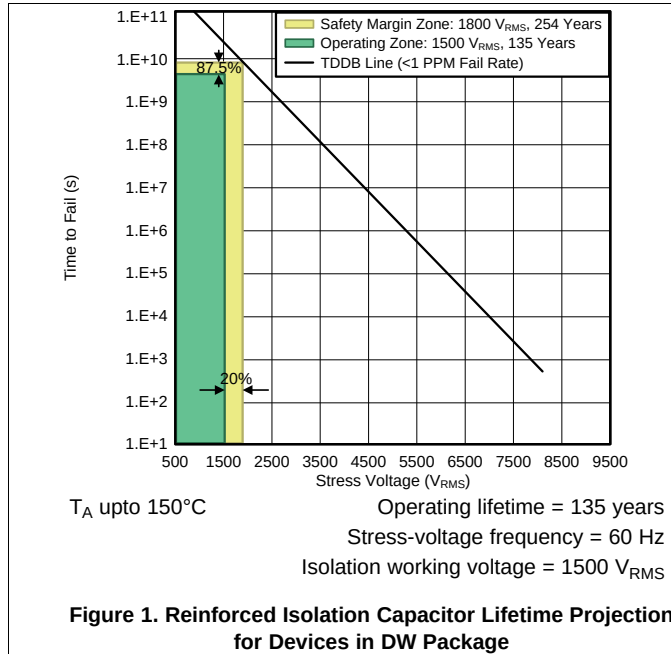
6.17 Switching Characteristics—2.5-V Supply

 $V_{CC1} = V_{CC2} = 2.5 \text{ V} \pm 10\%$ (over recommended operating conditions unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
t_{PLH} , t_{PHL}	Propagation delay time	See Figure 13	7.5	11.7	17.5	ns
PWD	Pulse width distortion ⁽¹⁾ $ t_{PHL} - t_{PLH} $			0.66	4.2	ns
$t_{sk(o)}$	Channel-to-channel output skew time ⁽²⁾	Same-direction Channels			2.2	ns
$t_{sk(pp)}$	Part-to-part skew time ⁽³⁾				4.5	ns
t_r	Output signal rise time	See Figure 13		1	3.5	ns
t_f	Output signal fall time			1.2	3.5	ns
t_{PHZ}	Disable propagation delay, high-to-high impedance output	See Figure 14		22	45	ns
t_{PLZ}	Disable propagation delay, low-to-high impedance output			22	45	ns
t_{PZH}	Enable propagation delay, high impedance-to-high output for ISO7831			18	45	ns
	Enable propagation delay, high impedance-to-high output for ISO7831F			2	2.5	μs
t_{PZL}	Enable propagation delay, high impedance-to-low output for ISO7831			2	2.5	μs
	Enable propagation delay, high impedance-to-low output for ISO7831F			18	45	ns
t_{DO}	Default output delay time from input power loss	Measured from the time V_{CC} goes below 1.7 V. See Figure 15		0.2	9	μs
t_e	Time interval error	$2^{16} - 1$ PRBS data at 100 Mbps		0.91		ns

- (1) Also known as pulse skew.
- (2) $t_{sk(o)}$ is the skew between outputs of a single device with all driving inputs connected together and the outputs switching in the same direction while driving identical loads.
- (3) $t_{sk(pp)}$ is the magnitude of the difference in propagation delay times between any terminals of different devices switching in the same direction while operating at identical supply voltages, temperature, input signals and loads.

6.18 Insulation Characteristics Curves



6.19 Typical Characteristics

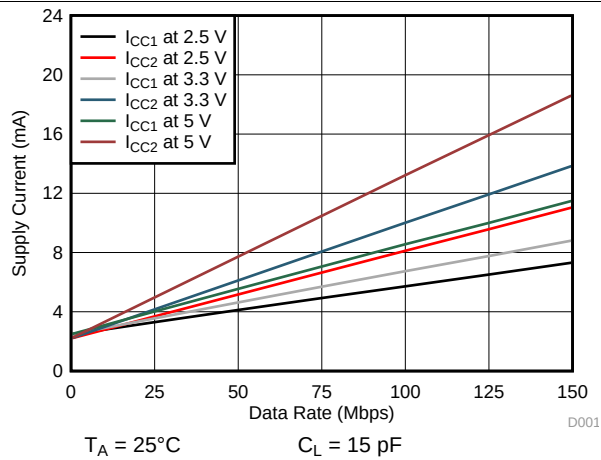


Figure 7. Supply Current vs Data Rate (With 15-pF Load)

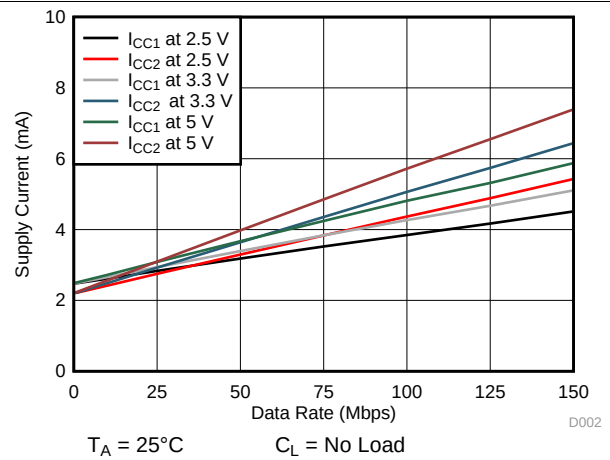


Figure 8. Supply Current vs Data Rate (With No Load)

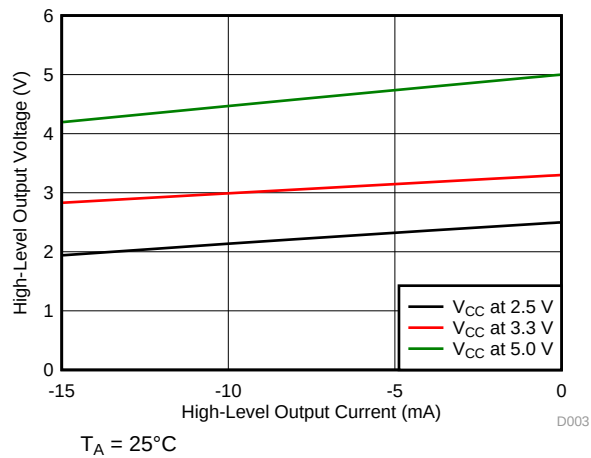


Figure 9. High-Level Output Voltage vs High-level Output Current

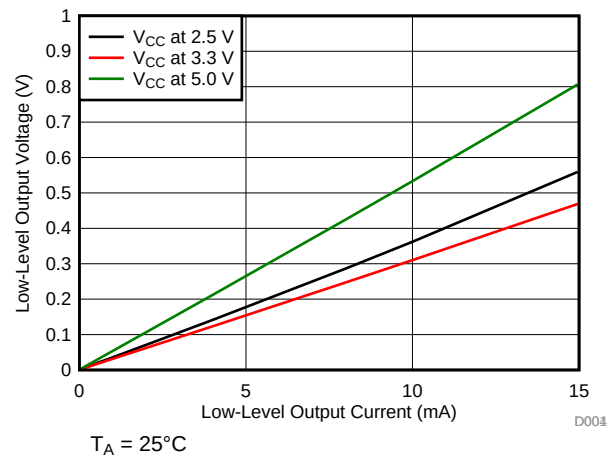


Figure 10. Low-Level Output Voltage vs Low-Level Output Current

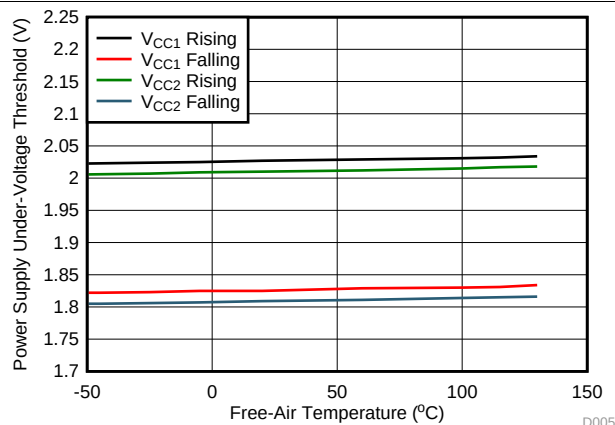


Figure 11. Power Supply Undervoltage Threshold vs Free-Air Temperature

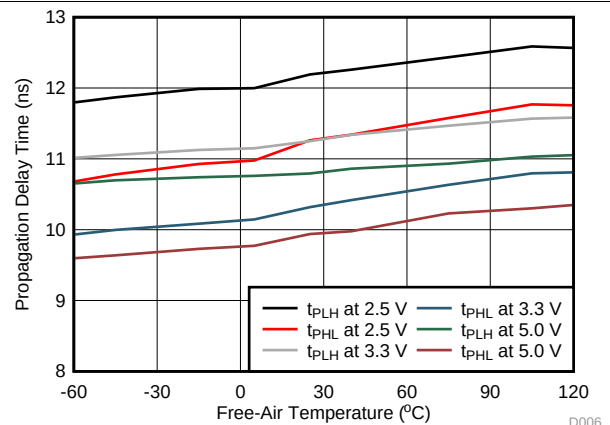
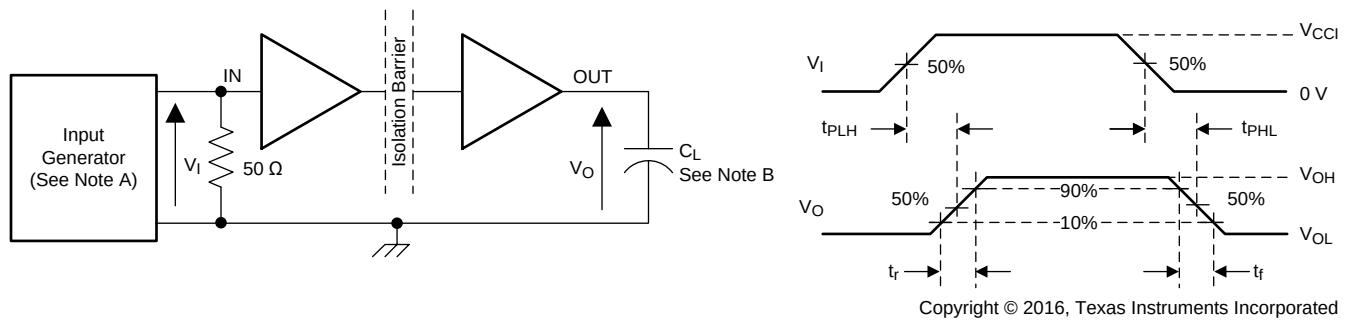


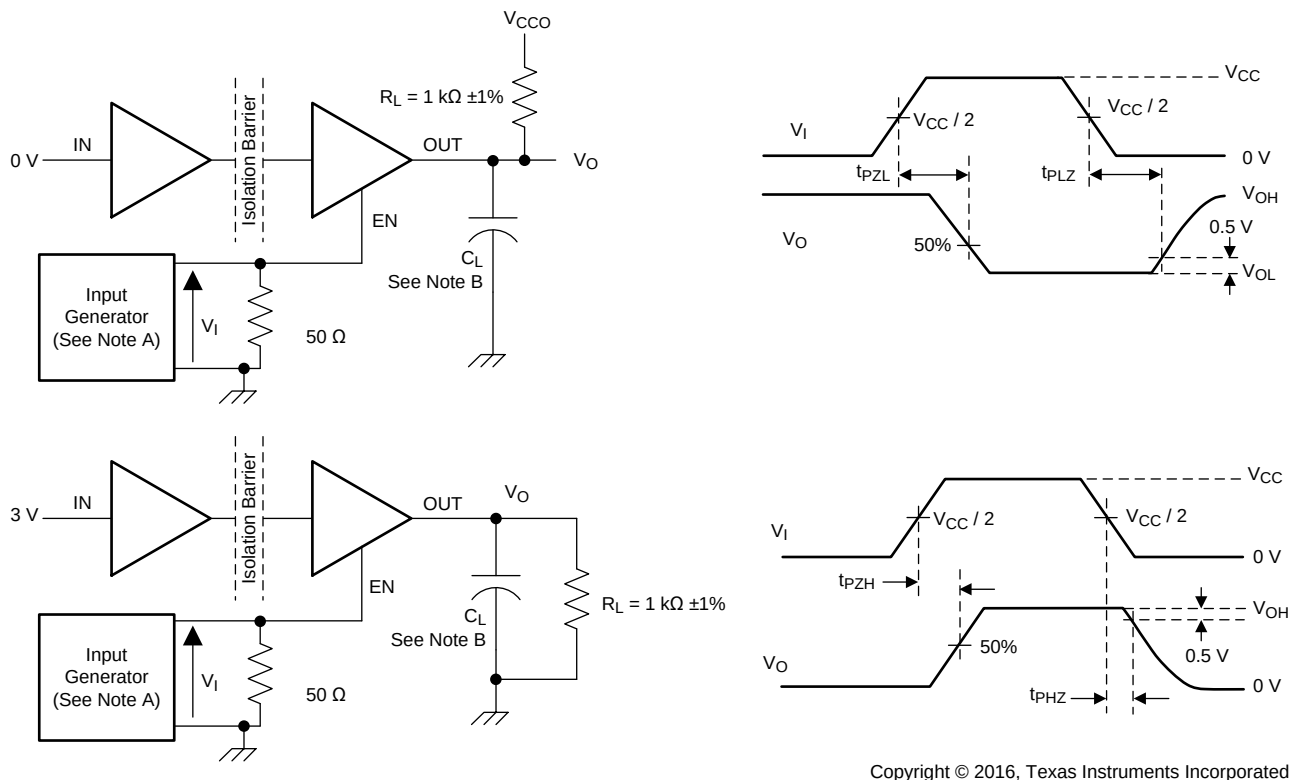
Figure 12. Propagation Delay Time vs Free-Air Temperature

7 Parameter Measurement Information



- A. The input pulse is supplied by a generator having the following characteristics: $\text{PRR} \leq 50 \text{ kHz}$, 50% duty cycle, $t_r \leq 3 \text{ ns}$, $t_f \leq 3 \text{ ns}$, $Z_O = 50 \Omega$. At the input, 50Ω resistor is required to terminate Input Generator signal. It is not needed in actual application.
- B. $C_L = 15 \text{ pF}$ and includes instrumentation and fixture capacitance within $\pm 20\%$.

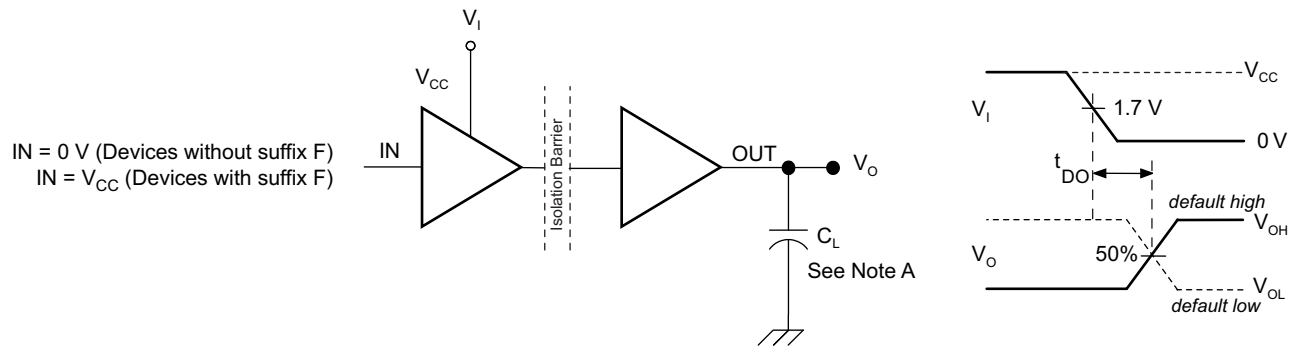
Figure 13. Switching Characteristics Test Circuit and Voltage Waveforms



- A. The input pulse is supplied by a generator having the following characteristics: $\text{PRR} \leq 10 \text{ kHz}$, 50% duty cycle, $t_r \leq 3 \text{ ns}$, $t_f \leq 3 \text{ ns}$, $Z_O = 50 \Omega$.
- B. $C_L = 15 \text{ pF}$ and includes instrumentation and fixture capacitance within $\pm 20\%$.

Figure 14. Enable/Disable Propagation Delay Time Test Circuit and Waveform

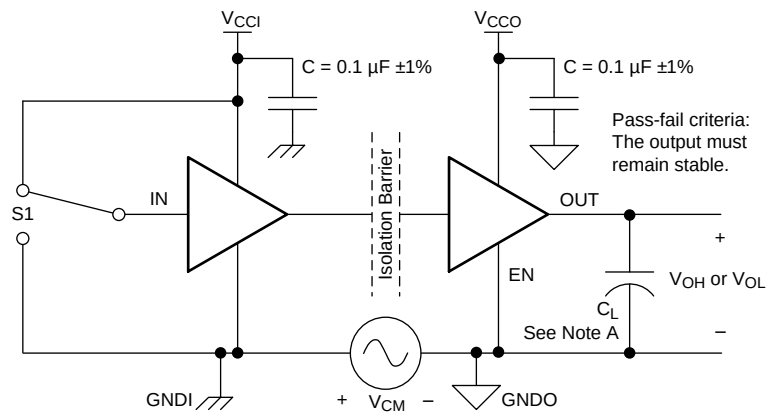
Parameter Measurement Information (continued)



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- A. $C_L = 15$ pF and includes instrumentation and fixture capacitance within $\pm 20\%$.

Figure 15. Default Output Delay Time Test Circuit and Voltage Waveforms



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- A. $C_L = 15$ pF and includes instrumentation and fixture capacitance within $\pm 20\%$.

Figure 16. Common-Mode Transient Immunity Test Circuit

8 Detailed Description

8.1 Overview

The ISO7831x device has an ON-OFF keying (OOK) modulation scheme to transmit the digital data across a silicon dioxide based isolation barrier. The transmitter sends a high frequency carrier across the barrier to represent one digital state and sends no signal to represent the other digital state. The receiver demodulates the signal after advanced signal conditioning and produces the output through a buffer stage. If the EN pin is low then the output goes to high impedance. The ISO7831x device also incorporates advanced circuit techniques to maximize the CMTI performance and minimize the radiated emissions because of the high frequency carrier and IO buffer switching. The conceptual block diagram of a digital capacitive isolator, [Figure 17](#), shows a functional block diagram of a typical channel.

8.2 Functional Block Diagram

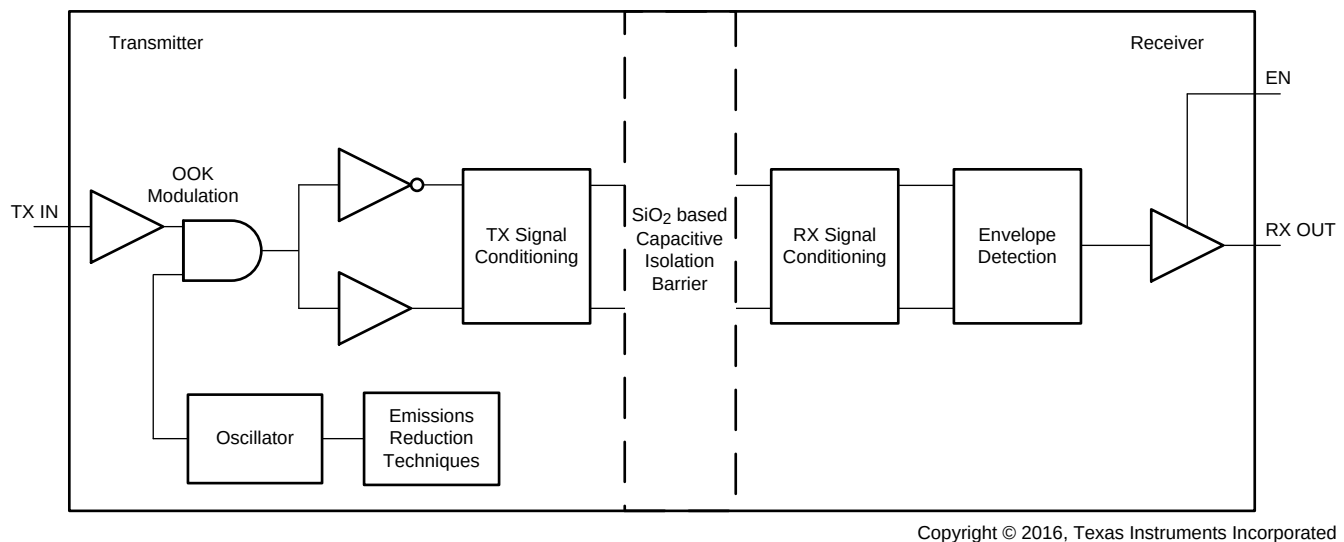


Figure 17. Conceptual Block Diagram of a Digital Capacitive Isolator

[Figure 18](#) shows a conceptual detail of how the ON-OFF keying scheme works.

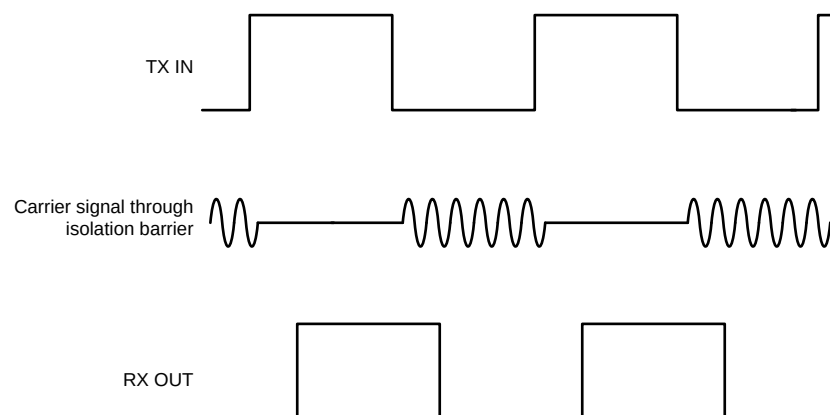


Figure 18. On-Off Keying (OOK) Based Modulation Scheme

8.3 Feature Description

Table 1 provides an overview of the device features.

Table 1. Device Features

PART NUMBER	CHANNEL DIRECTION	RATED ISOLATION	MAXIMUM DATA RATE	DEFAULT OUTPUT
ISO7831	2 Forward, 1 Reverse	5700 V _{RMS} / 8000 V _{PK} ⁽¹⁾	100 Mbps	High
ISO7831F	2 Forward, 1 Reverse	5700 V _{RMS} / 8000 V _{PK} ⁽¹⁾	100 Mbps	Low

(1) See the [Regulatory Information](#) section for detailed isolation ratings.

8.3.1 Electromagnetic Compatibility (EMC) Considerations

Many applications in harsh industrial environment are sensitive to disturbances such as electrostatic discharge (ESD), electrical fast transient (EFT), surge and electromagnetic emissions. These electromagnetic disturbances are regulated by international standards such as IEC 61000-4-x and CISPR 22. Although system-level performance and reliability depends, to a large extent, on the application board design and layout, the ISO7831x device incorporates many chip-level design improvements for overall system robustness. Some of these improvements include:

- Robust ESD protection cells for input and output signal pins and inter-chip bond pads.
- Low-resistance connectivity of ESD cells to supply and ground pins.
- Enhanced performance of high voltage isolation capacitor for better tolerance of ESD, EFT and surge events.
- Bigger on-chip decoupling capacitors to bypass undesirable high energy signals through a low impedance path.
- PMOS and NMOS devices isolated from each other by using guard rings to avoid triggering of parasitic SCRs.
- Reduced common mode currents across the isolation barrier by ensuring purely differential internal operation.

8.4 Device Functional Modes

Table 2 lists the ISO7831x functional modes.

Table 2. Function Table⁽¹⁾

V_{CCI}	V_{CCO}	INPUT (INx) ⁽²⁾	OUTPUT ENABLE (ENx)	OUTPUT (OUTx)	COMMENTS
PU	PU	H	H or open	H	Normal Operation: A channel output assumes the logic state of the input.
		L	H or open	L	
		Open	H or open	Default	Default mode: When INx is open, the corresponding channel output goes to its default logic state. Default is High for ISO7831 and Low for ISO7831F.
X	PU	X	L	Z	A low value of output enable causes the outputs to be high-impedance
PD	PU	X	H or open	Default	Default mode: When V_{CCI} is unpowered, a channel output assumes the logic state based on the selected default option. Default is High for ISO7831 and Low for ISO7831F. When V_{CCI} transitions from unpowered to powered-up, a channel output assumes the logic state of the input. When V_{CCI} transitions from powered-up to unpowered, channel output assumes the selected default state.
X	PD	X	X	Undetermined	When V_{CCO} is unpowered, a channel output state is undetermined ⁽³⁾ . When V_{CCO} transitions from unpowered to powered-up, a channel output assumes the logic state of the input

(1) V_{CCI} = Input-side V_{CC} ; V_{CCO} = Output-side V_{CC} ; PU = Powered up ($V_{CC} \geq 2.25$ V); PD = Powered down ($V_{CC} \leq 1.7$ V); X = Irrelevant; H = High level; L = Low level ; Z = High Impedance

(2) A strongly driven input signal can weakly power the floating V_{CC} via an internal protection diode and cause undetermined output.

(3) The outputs are in undetermined state when $1.7\text{ V} < V_{CCI}$, $V_{CCO} < 2.25\text{ V}$.

8.4.1 Device I/O Schematics

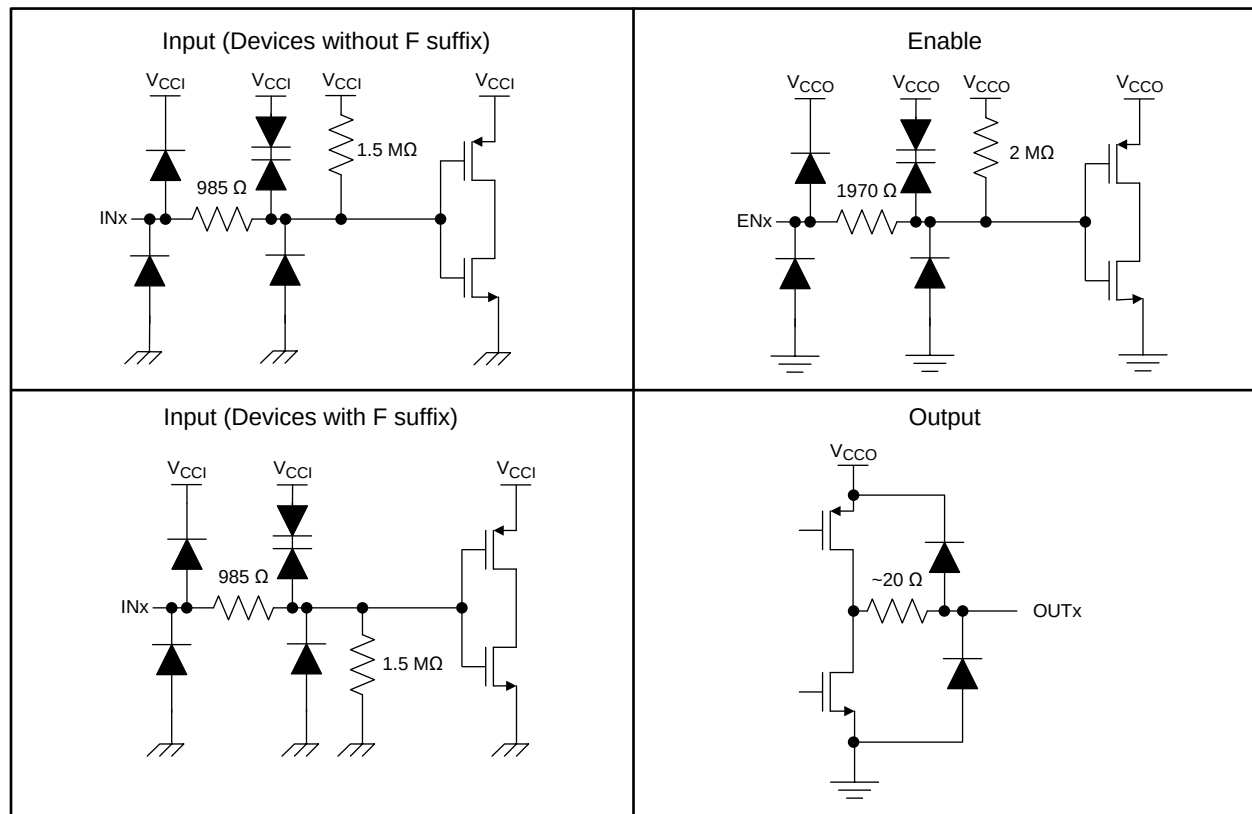


Figure 19. Device I/O Schematics

9 Application and Implementation

NOTE

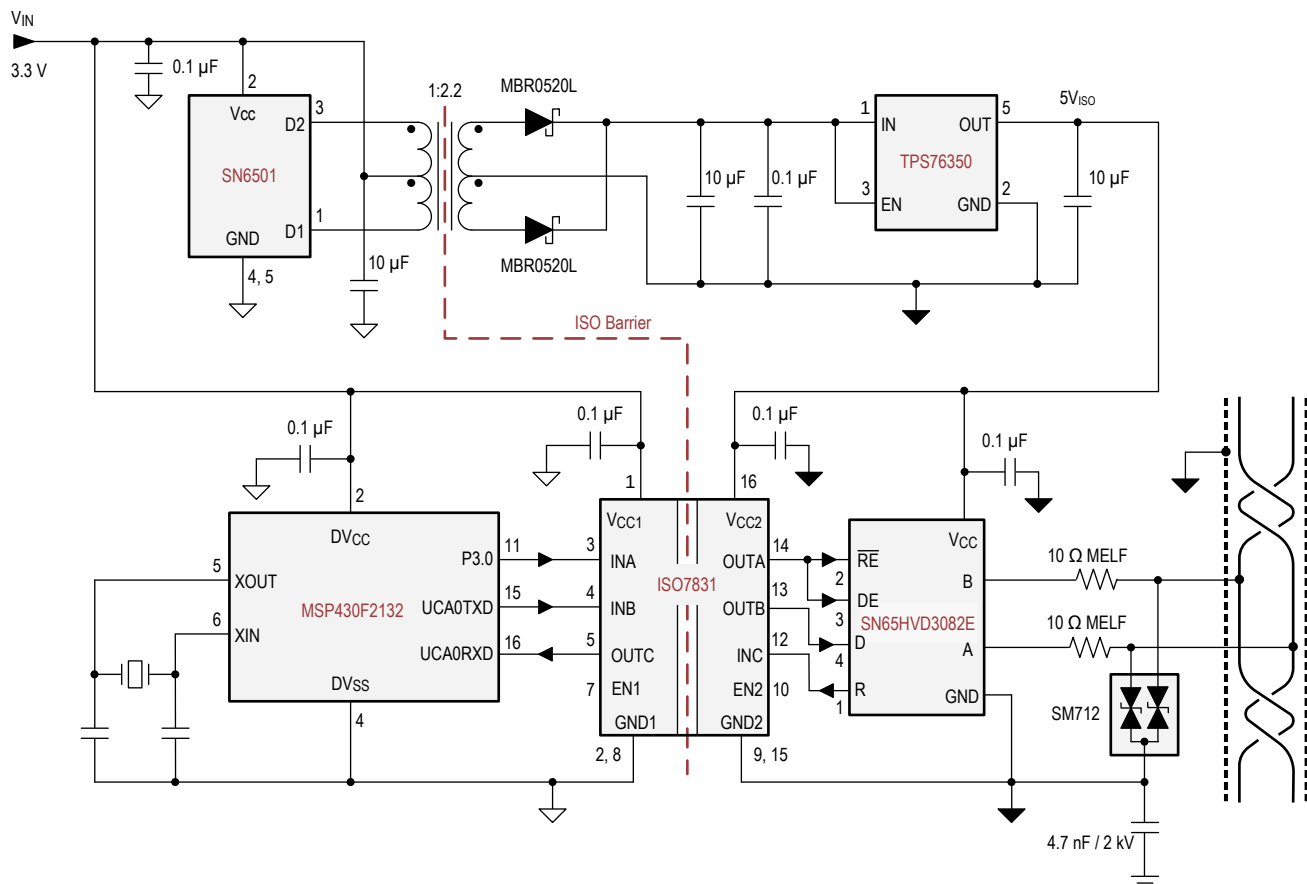
Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

9.1 Application Information

The ISO7831x device is a high-performance, triple-channel digital isolator with 5.7-kV_{RMS} isolation voltage. The device comes with enable pins on each side which can be used to put the respective outputs in high impedance for multi-master driving applications and reduce power consumption. The ISO7831x device uses single-ended CMOS-logic switching technology. The supply voltage range is from 2.25 V to 5.5 V for both supplies, V_{CC1} and V_{CC2}. When designing with digital isolators, keep in mind that because of the single-ended design structure, digital isolators do not conform to any specific interface standard and are only intended for isolating single-ended CMOS or TTL digital signal lines. The isolator is typically placed between the data controller (that is, μ C or UART), and a data converter or a line transceiver, regardless of the interface type or standard.

9.2 Typical Application

Figure 20 shows the isolated RS-485 interface application circuit.



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Figure 20. Isolated RS-485 Circuit

Typical Application (continued)

9.2.1 Design Requirements

For this design example, use the parameters listed in [Table 3](#).

Table 3. Design Parameters

PARAMETER	VALUE
Supply voltage	2.25 to 5.5 V
Decoupling capacitor between V_{CC1} and GND1	0.1 μ F
Decoupling capacitor from V_{CC2} and GND2	0.1 μ F

9.2.2 Detailed Design Procedure

Unlike optocouplers, which require external components to improve performance, provide bias, or limit current, ISO7831x only requires two external bypass capacitors to operate.

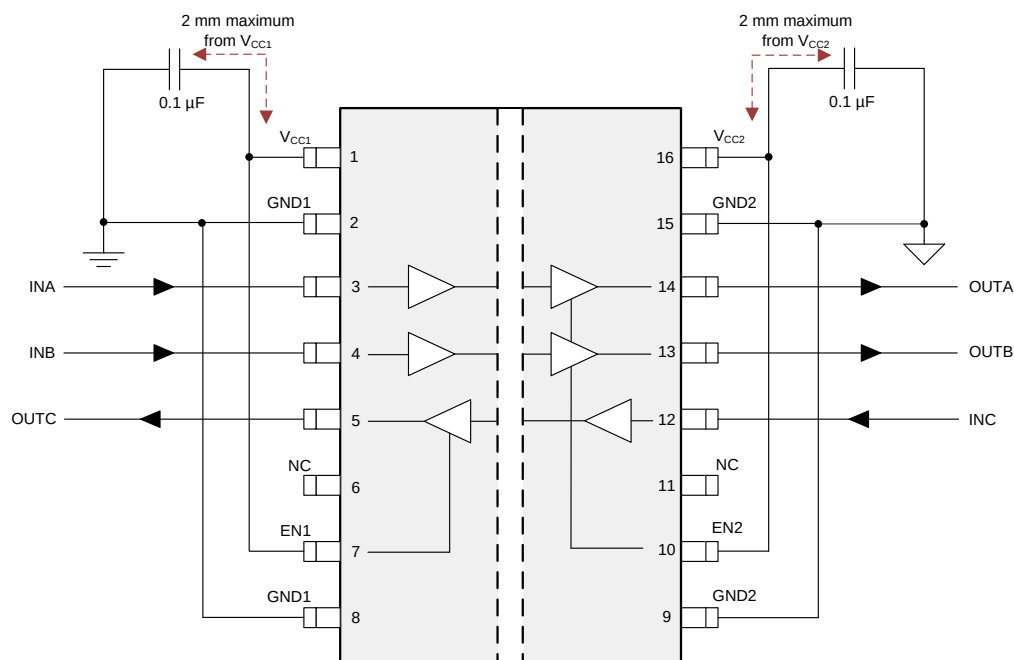


Figure 21. Typical ISO7831 Circuit Hook-up

9.2.3 Application Curve

The following typical eye diagram of the ISO7831x device indicates low jitter and wide open eye at the maximum data rate of 100 Mbps.

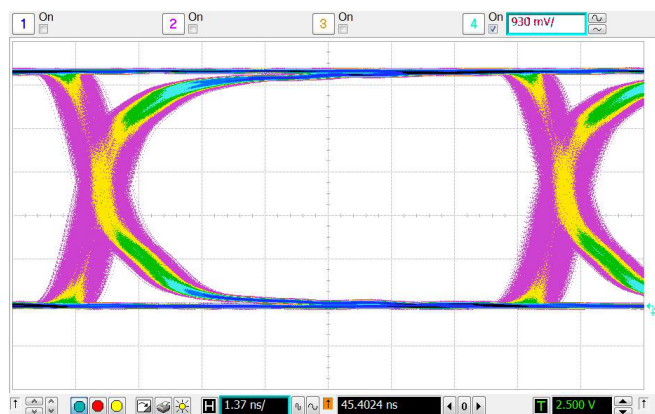


Figure 22. Eye Diagram at 100 Mbps PRBS, 5 V and 25°C

10 Power Supply Recommendations

To help ensure reliable operation at data rates and supply voltages, a 0.1-μF bypass capacitor is recommended at input and output supply pins (V_{CC1} and V_{CC2}). The capacitors should be placed as close to the supply pins as possible. If only a single primary-side power supply is available in an application, isolated power can be generated for the secondary-side with the help of a transformer driver such as Texas Instruments' [SN6501](#). For such applications, detailed power supply design and transformer selection recommendations are available in SN6501 data sheet ([SLLSEA0](#)).

11 Layout

11.1 Layout Guidelines

A minimum of four layers is required to accomplish a low EMI PCB design (see [Figure 23](#)). Layer stacking should be in the following order (top-to-bottom): high-speed signal layer, ground plane, power plane and low-frequency signal layer.

- Routing the high-speed traces on the top layer avoids the use of vias (and the introduction of their inductances) and allows for clean interconnects between the isolator and the transmitter and receiver circuits of the data link.
- Placing a solid ground plane next to the high-speed signal layer establishes controlled impedance for transmission line interconnects and provides an excellent low-inductance path for the return current flow.
- Placing the power plane next to the ground plane creates additional high-frequency bypass capacitance of approximately 100 pF/inch².
- Routing the slower speed control signals on the bottom layer allows for greater flexibility as these signal links usually have margin to tolerate discontinuities such as vias.

If an additional supply voltage plane or signal layer is needed, add a second power or ground plane system to the stack to keep it symmetrical. This makes the stack mechanically stable and prevents it from warping. Also the power and ground plane of each power system can be placed closer together, thus increasing the high-frequency bypass capacitance significantly.

For detailed layout recommendations, see the application note, *Digital Isolator Design Guide* ([SLLA284](#)).

11.1.1 PCB Material

For digital circuit boards operating at less than 150 Mbps (or rise and fall times greater than 1 ns) and trace lengths of up to 10 inches, use standard FR-4 UL94V-0 printed circuit board. This PCB is preferred over cheaper alternatives because of lower dielectric losses at high frequencies, less moisture absorption, greater strength and stiffness, and the self-extinguishing flammability-characteristics.

11.2 Layout Example

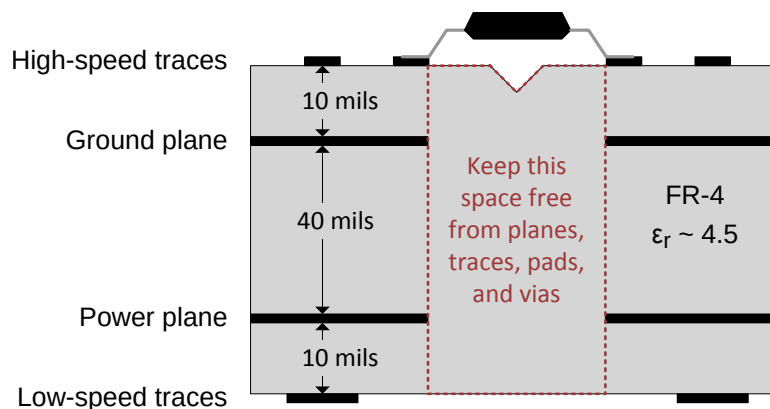


Figure 23. Layout Example Schematic

12 Device and Documentation Support

12.1 Documentation Support

12.1.1 Related Documentation

For related documentation see the following:

- *Digital Isolator Design Guide*, [SLLA284](#)
- *Isolation Glossary*, [SLLA353](#)
- *SN6501 Transformer Driver for Isolated Power Supplies*, [SLLSEA0](#)
- *SNx5HVD308xE Low-Power RS-485 Transceivers, Available in a Small MSOP-8 Package*, [SLLS562](#)
- *TPS76350 Low-Power 150-mA Low-Dropout Linear Regulators*, [SLVS181](#)
- *MSP430F2132 Mixed Signal Microcontroller*, [SLAS578](#)

12.2 Related Links

The table below lists quick access links. Categories include technical documents, support and community resources, tools and software, and quick access to sample or buy.

Table 4. Related Links

PARTS	PRODUCT FOLDER	SAMPLE & BUY	TECHNICAL DOCUMENTS	TOOLS & SOFTWARE	SUPPORT & COMMUNITY
ISO7831	Click here	Click here	Click here	Click here	Click here
ISO7831F	Click here	Click here	Click here	Click here	Click here

12.3 Receiving Notification of Documentation Updates

To receive notification of documentation updates — go to the product folder for your device on ti.com. In the upper right-hand corner, click the *Alert me* button to register and receive a weekly digest of product information that has changed (if any). For change details, check the revision history of any revised document.

12.4 Community Resources

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's [Terms of Use](#).

TI E2E™ Online Community *TI's Engineer-to-Engineer (E2E) Community*. Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

Design Support *TI's Design Support* Quickly find helpful E2E forums along with design support tools and contact information for technical support.

12.5 Trademarks

E2E is a trademark of Texas Instruments.

All other trademarks are the property of their respective owners.

12.6 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

12.7 Glossary

[SLYZ022](#) — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

13 Mechanical, Packaging, and Orderable Information

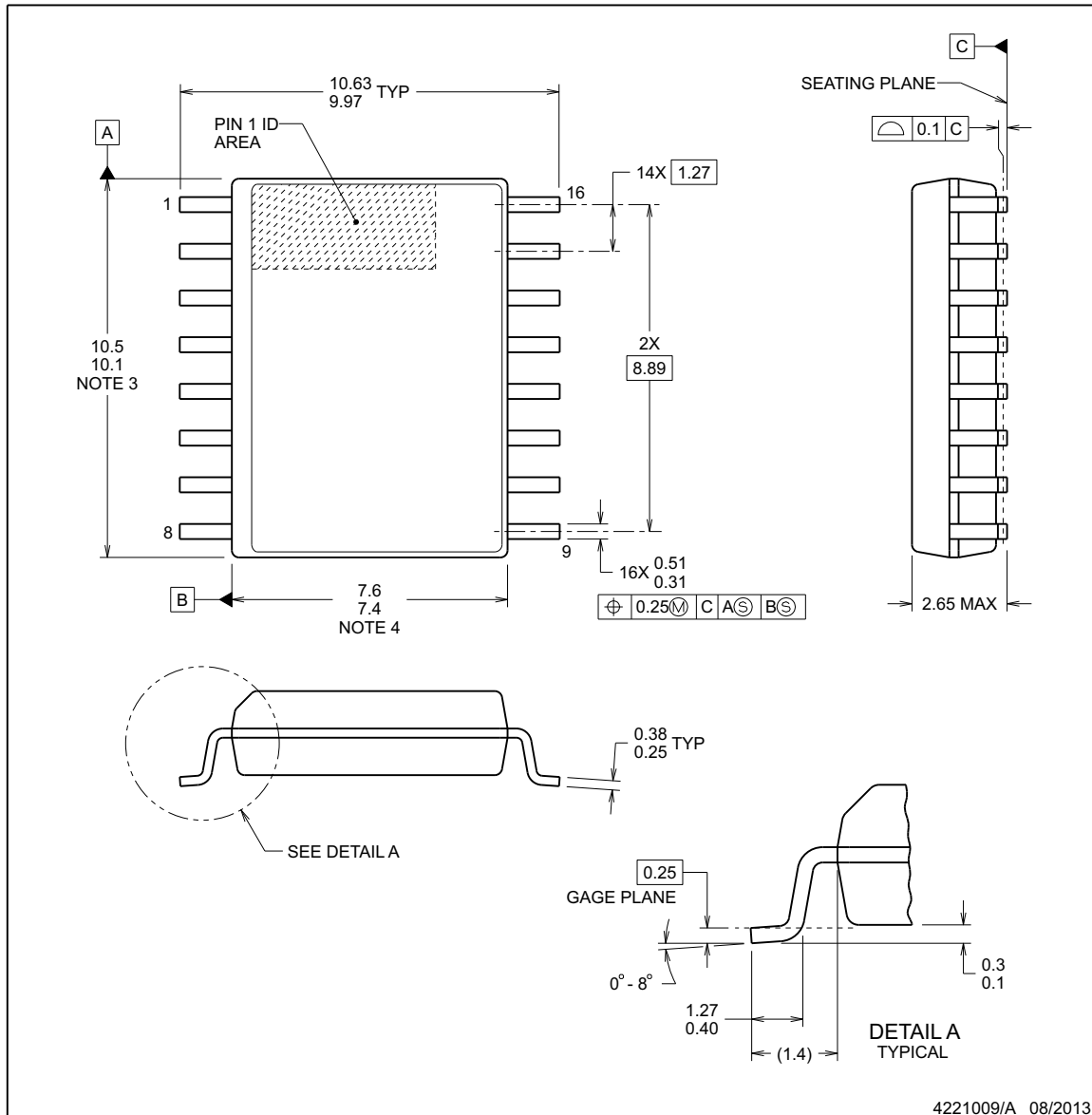
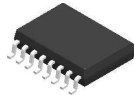
The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGE OUTLINE

DW0016B

SOIC - 2.65 mm max height

SOIC



4221009/A 08/2013

NOTES:

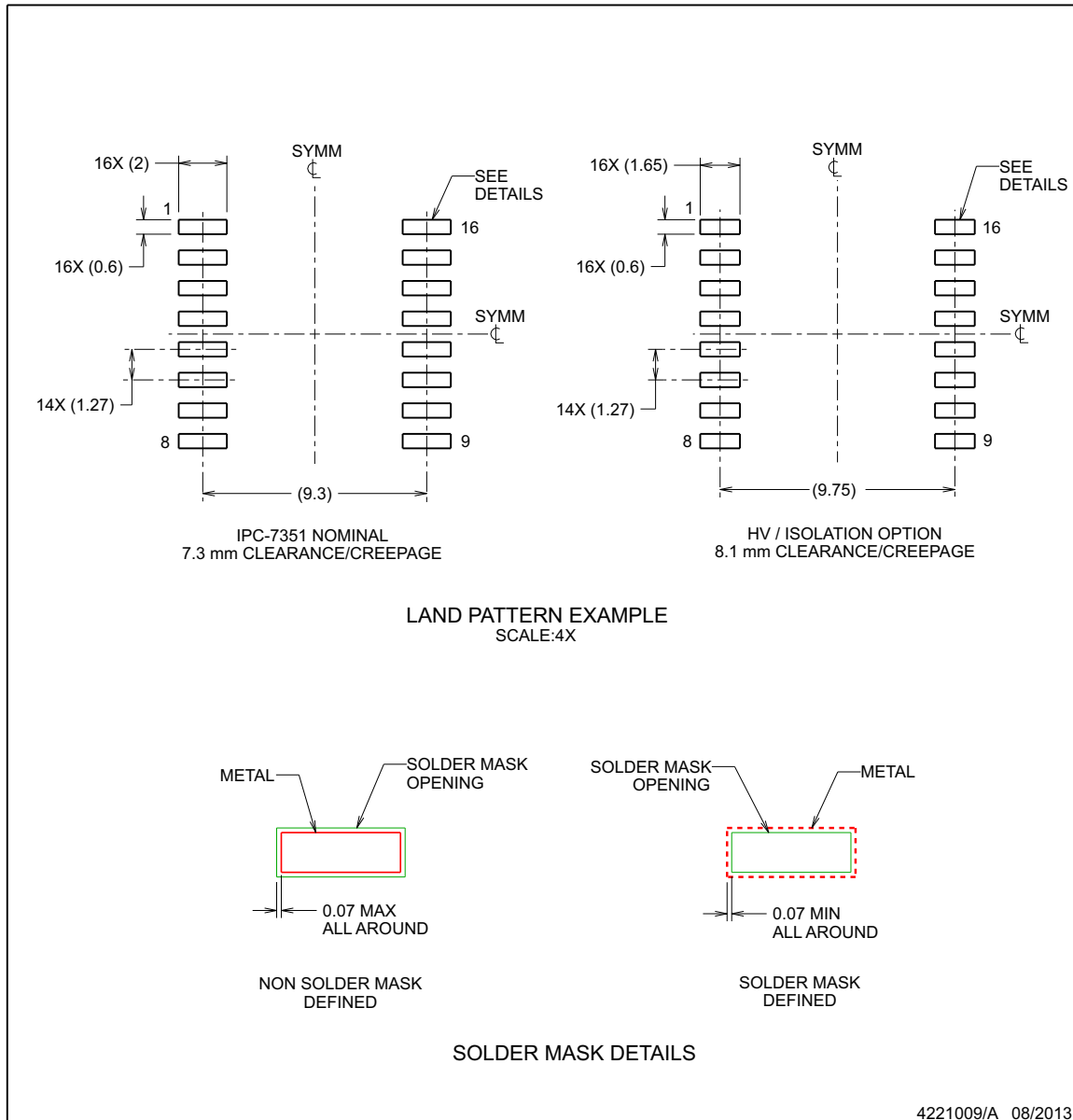
1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm, per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm, per side.
5. Reference JEDEC registration MO-013, variation AA.

EXAMPLE BOARD LAYOUT

DW0016B

SOIC - 2.65 mm max height

SOIC



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

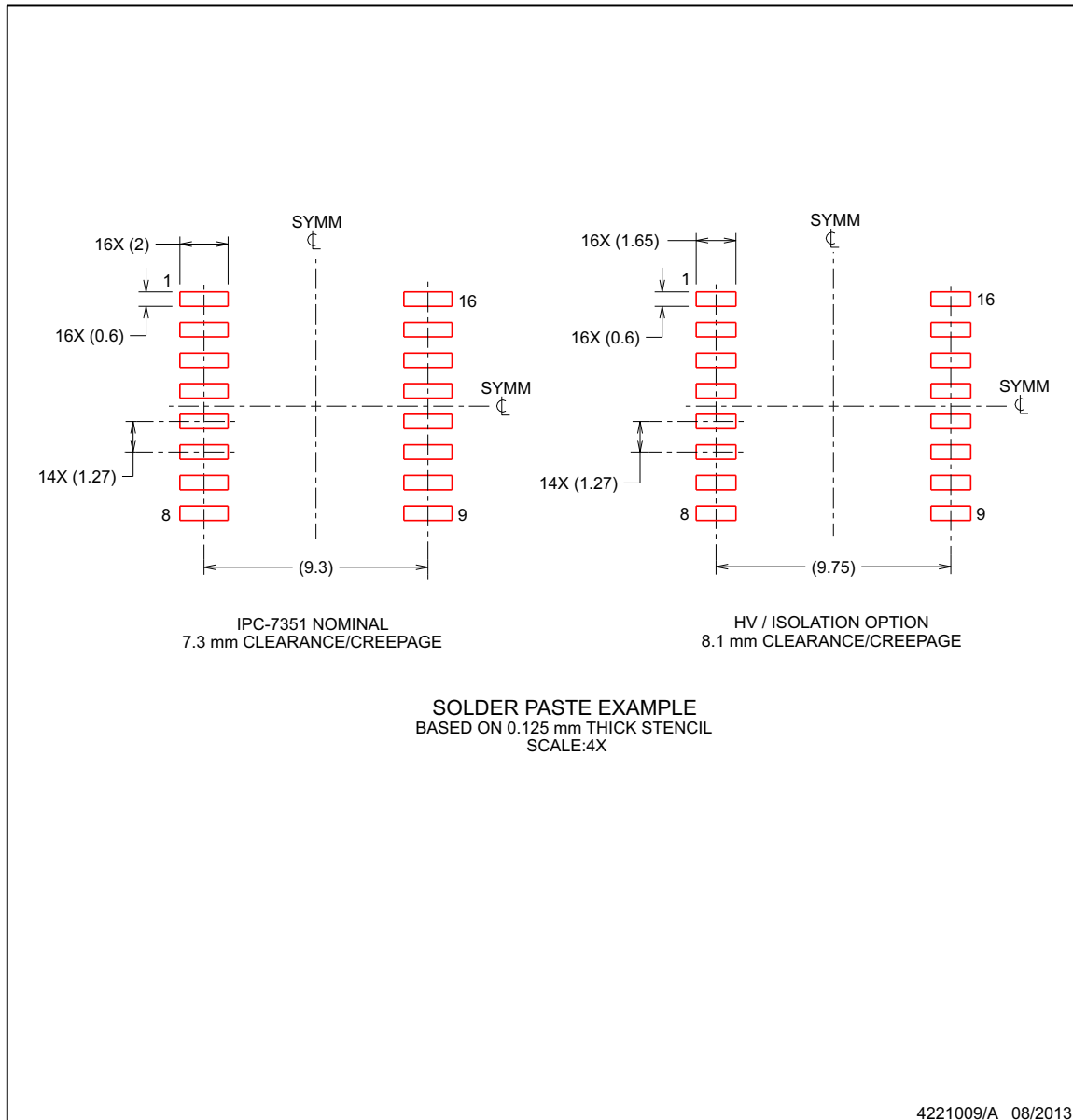
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

DW0016B

SOIC - 2.65 mm max height

SOIC

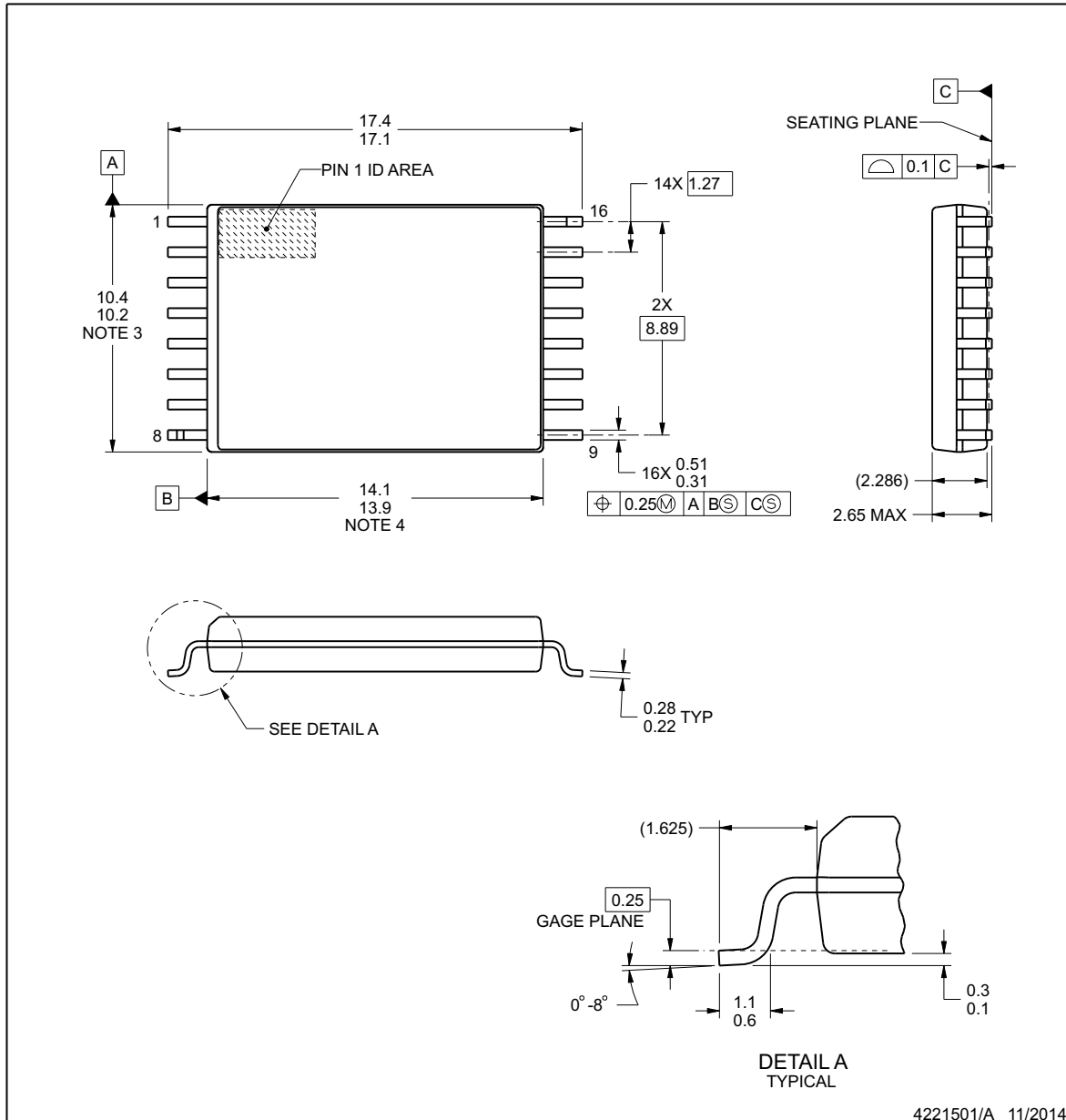


NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.


DWW0016A
PACKAGE OUTLINE
SOIC - 2.65 mm max height

PLASTIC SMALL OUTLINE


NOTES:

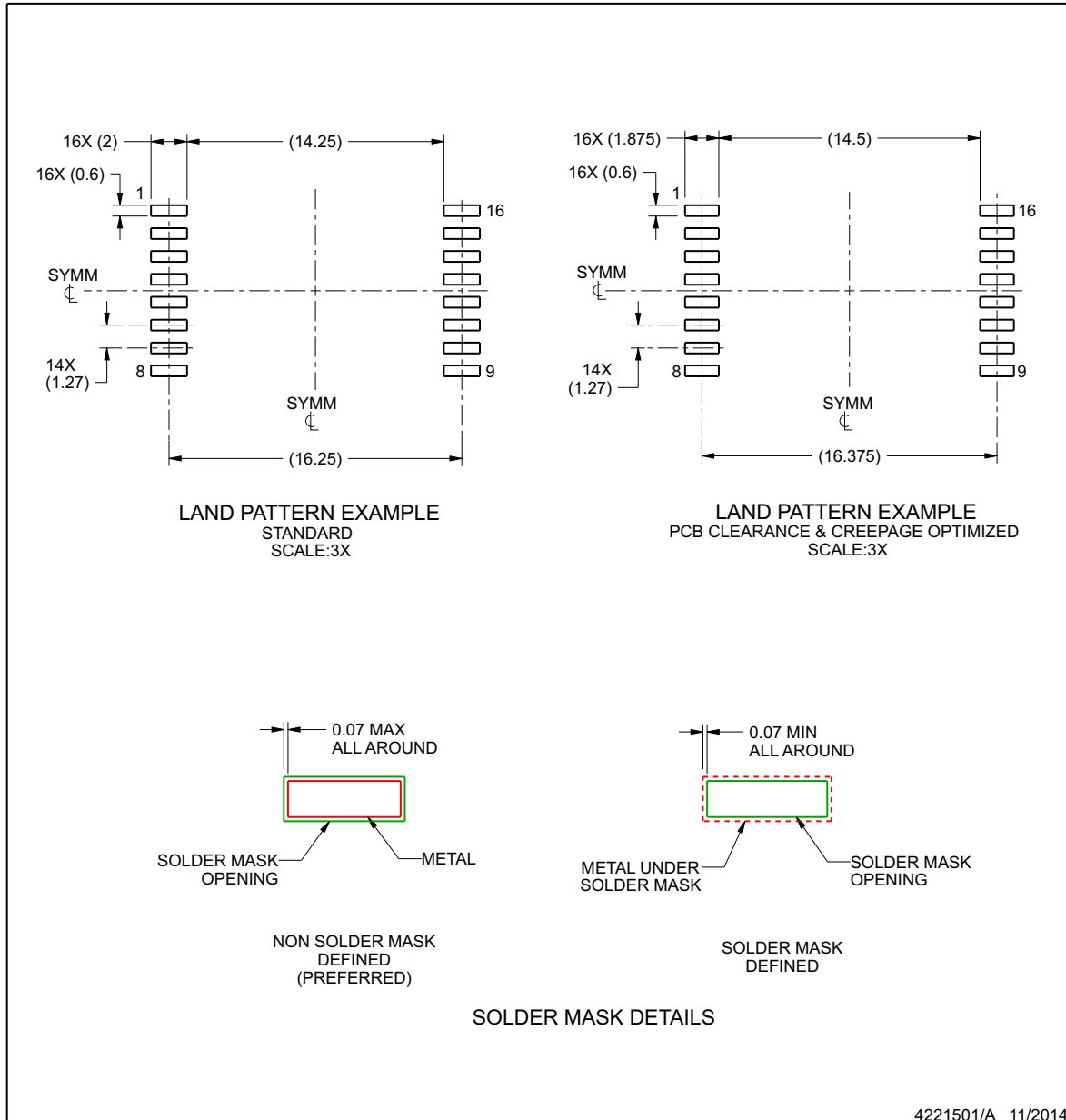
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash.

EXAMPLE BOARD LAYOUT

DWW0016A

SOIC - 2.65 mm max height

PLASTIC SMALL OUTLINE



NOTES: (continued)

5. Publication IPC-7351 may have alternate designs.

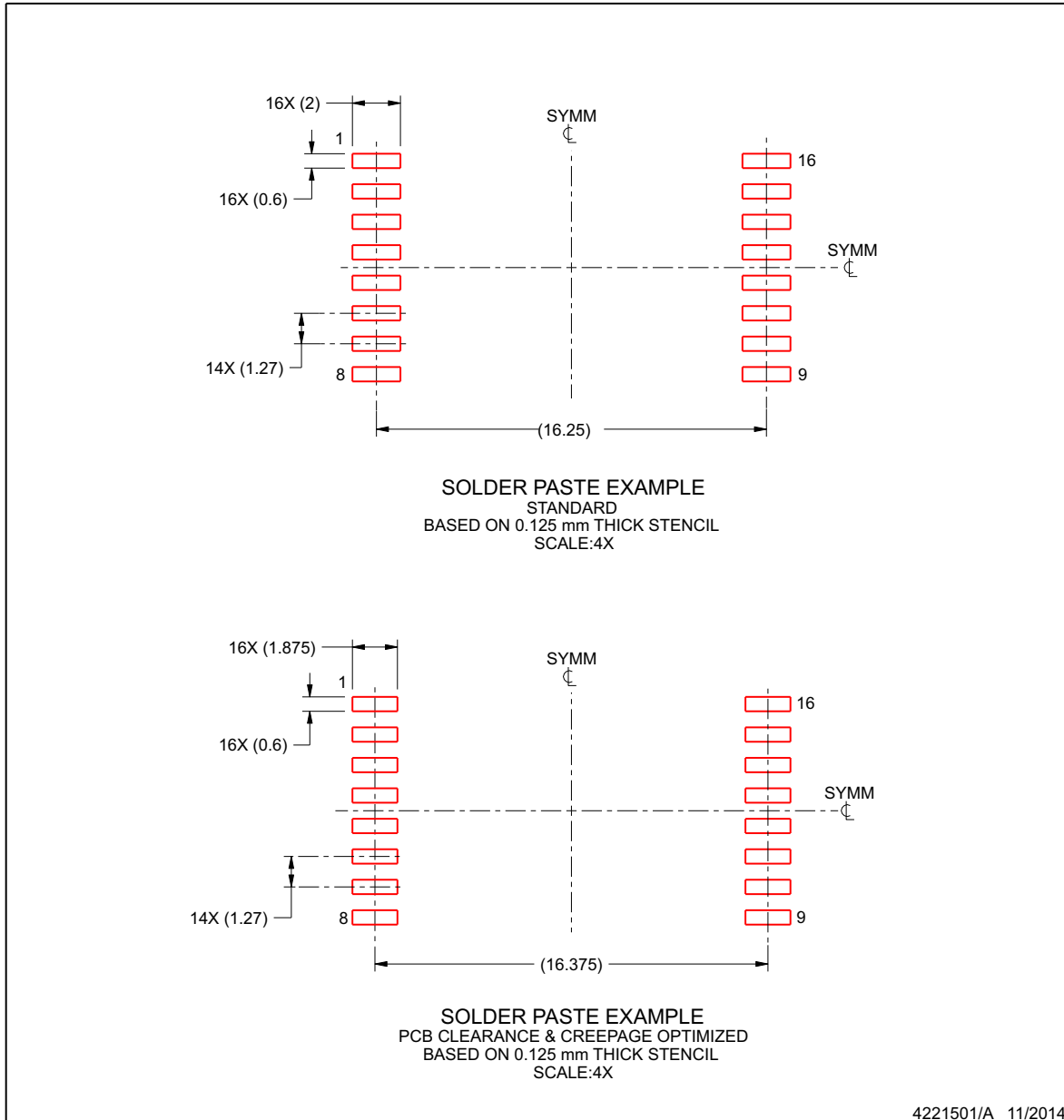
6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

DWW0016A

SOIC - 2.65 mm max height

PLASTIC SMALL OUTLINE



NOTES: (continued)

7. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
8. Board assembly site may have different recommendations for stencil design.

PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package Pins	Package qty Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
ISO7831DW	Active	Production	SOIC (DW) 16	40 TUBE	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	ISO7831
ISO7831DW.A	Active	Production	SOIC (DW) 16	40 TUBE	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	ISO7831
ISO7831DW.B	Active	Production	SOIC (DW) 16	40 TUBE	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	ISO7831
ISO7831DWR	Active	Production	SOIC (DW) 16	2000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	ISO7831
ISO7831DWR.A	Active	Production	SOIC (DW) 16	2000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	ISO7831
ISO7831DWR.B	Active	Production	SOIC (DW) 16	2000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	ISO7831
ISO7831DWW	Active	Production	SOIC (DWW) 16	45 TUBE	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	ISO7831
ISO7831DWW.A	Active	Production	SOIC (DWW) 16	45 TUBE	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	ISO7831
ISO7831DWW.B	Active	Production	SOIC (DWW) 16	45 TUBE	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	ISO7831
ISO7831DWR	Active	Production	SOIC (DWW) 16	1000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	ISO7831
ISO7831DWR.A	Active	Production	SOIC (DWW) 16	1000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	ISO7831
ISO7831DWR.B	Active	Production	SOIC (DWW) 16	1000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	ISO7831
ISO7831FDW	Active	Production	SOIC (DW) 16	40 TUBE	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	ISO7831F
ISO7831FDW.A	Active	Production	SOIC (DW) 16	40 TUBE	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	ISO7831F
ISO7831FDW.B	Active	Production	SOIC (DW) 16	40 TUBE	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	ISO7831F
ISO7831FDWR	Active	Production	SOIC (DW) 16	2000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	ISO7831F
ISO7831FDWR.A	Active	Production	SOIC (DW) 16	2000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	ISO7831F
ISO7831FDWR.B	Active	Production	SOIC (DW) 16	2000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	ISO7831F
ISO7831FDWW	Active	Production	SOIC (DWW) 16	45 TUBE	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	ISO7831F
ISO7831FDWW.A	Active	Production	SOIC (DWW) 16	45 TUBE	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	ISO7831F
ISO7831FDWW.B	Active	Production	SOIC (DWW) 16	45 TUBE	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	ISO7831F
ISO7831FDWR	Active	Production	SOIC (DWW) 16	1000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	ISO7831F
ISO7831FDWR.A	Active	Production	SOIC (DWW) 16	1000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	ISO7831F
ISO7831FDWR.B	Active	Production	SOIC (DWW) 16	1000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	ISO7831F

⁽¹⁾ **Status:** For more details on status, see our [product life cycle](#).

⁽²⁾ **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

⁽³⁾ **RoHS values:** Yes, No, RoHS Exempt. See the [TI RoHS Statement](#) for additional information and value definition.

⁽⁴⁾ **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

⁽⁵⁾ **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

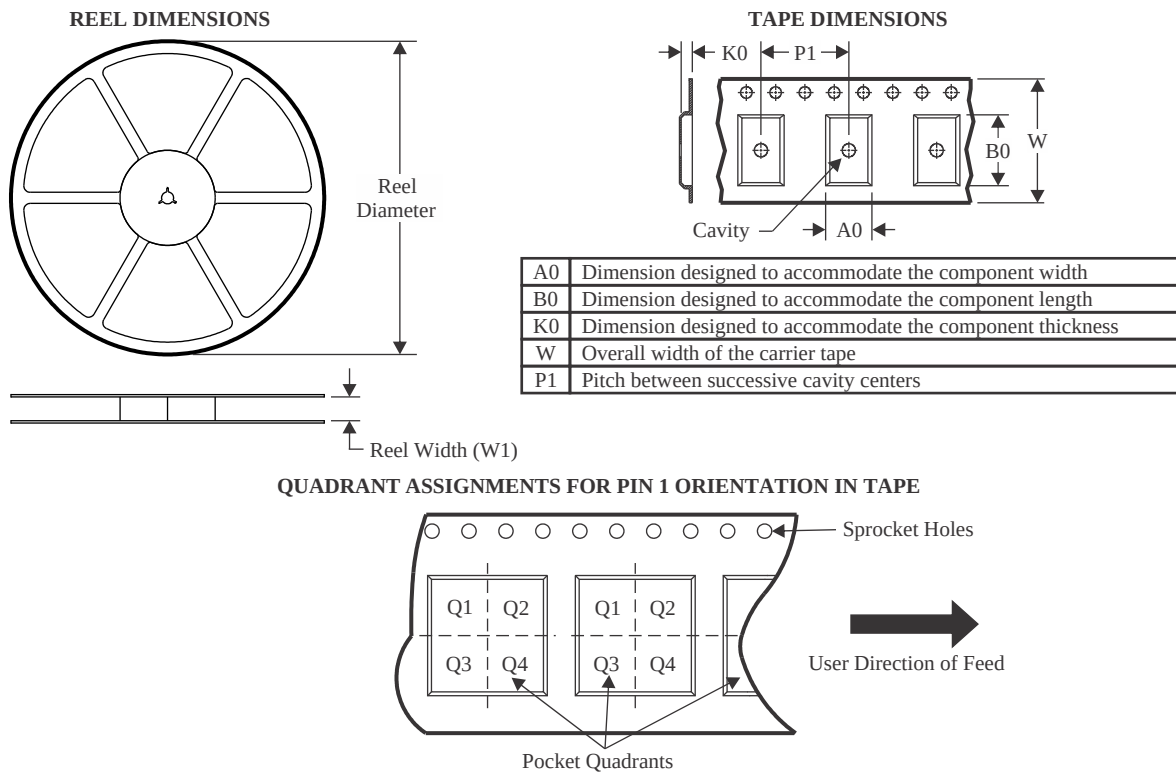
⁽⁶⁾ **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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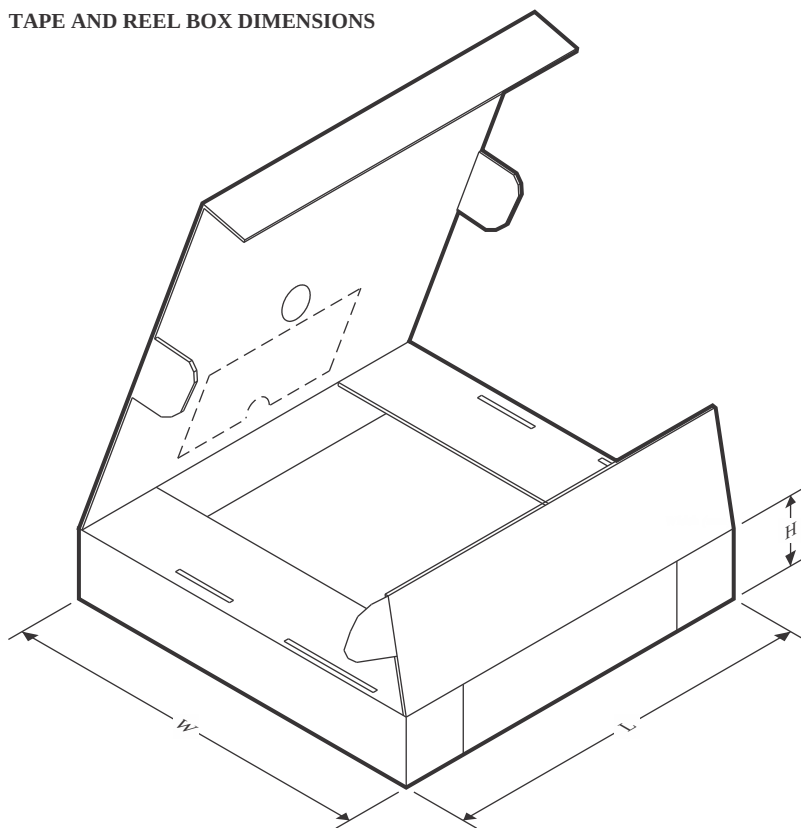
TAPE AND REEL INFORMATION



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
ISO7831DWR	SOIC	DW	16	2000	330.0	16.4	10.75	10.7	2.7	12.0	16.0	Q1
ISO7831DWWR	SOIC	DWW	16	1000	330.0	24.4	18.0	10.0	3.0	20.0	24.0	Q1
ISO7831FDWR	SOIC	DW	16	2000	330.0	16.4	10.75	10.7	2.7	12.0	16.0	Q1
ISO7831FDWWR	SOIC	DWW	16	1000	330.0	24.4	18.0	10.0	3.0	20.0	24.0	Q1

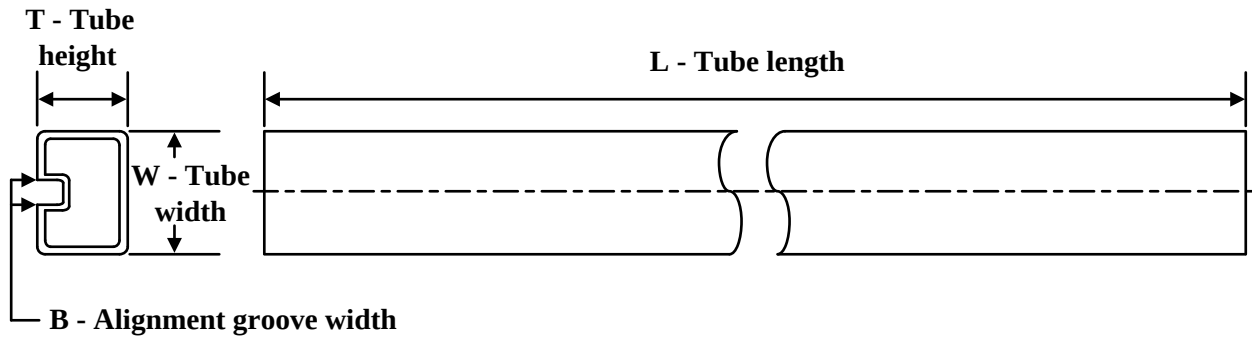
TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
ISO7831DWR	SOIC	DW	16	2000	350.0	350.0	43.0
ISO7831DWWR	SOIC	DWW	16	1000	350.0	350.0	43.0
ISO7831FDWR	SOIC	DW	16	2000	350.0	350.0	43.0
ISO7831FDWWR	SOIC	DWW	16	1000	350.0	350.0	43.0

TUBE



*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (μm)	B (mm)
ISO7831DW	DW	SOIC	16	40	506.98	12.7	4826	6.6
ISO7831DW.A	DW	SOIC	16	40	506.98	12.7	4826	6.6
ISO7831DW.B	DW	SOIC	16	40	506.98	12.7	4826	6.6
ISO7831DWW	DWW	SOIC	16	45	507	20	5000	9
ISO7831DWW.A	DWW	SOIC	16	45	507	20	5000	9
ISO7831DWW.B	DWW	SOIC	16	45	507	20	5000	9
ISO7831FDW	DW	SOIC	16	40	506.98	12.7	4826	6.6
ISO7831FDW.A	DW	SOIC	16	40	506.98	12.7	4826	6.6
ISO7831FDW.B	DW	SOIC	16	40	506.98	12.7	4826	6.6
ISO7831FDWW	DWW	SOIC	16	45	507	20	5000	9
ISO7831FDWW.A	DWW	SOIC	16	45	507	20	5000	9
ISO7831FDWW.B	DWW	SOIC	16	45	507	20	5000	9

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